NEAR EAST UNIVERSITY



Faculty of Engineering

Department of Electrical and Electronic Engineering

TELEREMOTE CONTROL WITH PLC

Graduation Project EE – 400

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Lefkoşa - 2003

ACKNOWLEDGEMENT

First I want to thank Özgür Cemal Özerdem to be my Supervisor. Under this guidance, I successfully overcome many difficulties and learn a lot about PLC with EE470 PLC and with EE315 cources. PLC depends greatly on technology . In each discussion, he explained my questions patiently and answered my questions quickly and in detail. He always help me a lot either in my study.

Thanks to faculty of Engineering for having such a good computational environment. I want to thank all my student friends in NEU. Being with them make my during educational in NEU full of fun.

I also special thanks to my sister and his husband (Neriman & Güney Ünsal) and my brother (Cengiz Kaptan) with their kind help. I could succesfully to perform computational problems. They always help me a lot eiher in my studies.

Finally I want to thank especially my families. Without their endeless support and love for me.

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ASTRACT

In this study, a system of teleremote circuit via telephone lines. For building up the system minimum needs are Programmable Logic Controller (PLC), active telephone line, and teleremote control circuit.

The teleremote control circuit enables us to control some appliances: on the other hand the programmable logic controller (PLC) is controlled by teleremote control circuit. Therefore if there is a telephone line the control of the appliances can be any where.

The circuit described here can be used to switch up to nine appliances (corresponding to the digits 1 through 9 of the telephone key-pad). The DTMF signals on the telephone instrument are used as control signals. The digit '0' in DTMF mode is used to toggle between the appliance mode and normal telephone operation mode. Thus the telephone can be used to switch on or switch off the appliances via Programmable Logic Controller (PLC) and driven relays.

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INTRODUCTION

The rapid developments in electronics have unstopply revolutionized the telecommunication and internet technology in recent years and have become a part of daily life, bringing in everything from Pampers to programmable logic devices. The rising usage of internet has been complemented with developments in communication technology.



Figure 1. Siemens S7 CPU212 PLC

Moreover, Telecommunication technologies start to invade the home to carry phone signals and comfort of telecommunication systems. These rapid developments show that internet based and telecommunication systems have had a huge role in home and business solutions nowadays and will have more in future.

Telecommunication technology allows companies to overcome many of the physical constraints that often prevent them from doing business in distant markets, which means that an a commerce market is fundamentally global (Choi and Whinston.1999).

By using the telephone code of lines are sent to telephone and control the equipment via PLC. Its possible doing the processes wherever you are.

The functional as follows:

• Calling of the destination number then destination number will answer automatically.

• By pressing numbers the control circuit will sent the information received from telephone lines to PLC for performing the processes.

-



Figure 2. Architecture

1. INTRODUCING THE PLC

1.1 What is PLC?

A PLC (programmable logic controller) is a small industrial computer which originally replaced the necessary sequential relay circuits for machine control. The PLC works by looking at its inputs and depending upon their state, turning on/off its outputs. It contained a program which executed a loop, scanning the inputs and taking actions based on these inputs. The user enters a program, usually via software, that gives the desired results.

PLCs are used in many "real world" applications. If there is industry present, chances are good that there is a PLC present. If you are involved in machining, packaging, material handling, automated assembly or countless other industries you are probably already using them. If you are not, you are wasting money and time. Almost any application that needs some type of electrical control has a need for a PLC.

A PLC, basically consists of two elements:

I. the central processing unit

II. the input/output system

I. The Central Processing Unit

The central processing unit (CPU) is the part of a programmable controller that retrieves, decodes, stores, and processes information. It also executes the control program stored in the PLC's memory. In essence, the CPU is the "brains" of a programmable controller. It functions much the same way the CPU of a regular computer does, except that it uses special instructions and coding to perform its functions.

The CPU has three parts:

- I. the processor
- II. the memory system
- III. the power supply

The processor is the section of the CPU that codes, decodes, and computes data. The memory system is the section of the CPU that stores both the control program and data from the equipment connected to the PLC. The power supply is the section that provides the PLC with the voltage and current it needs to operate.

II. The Input/Output System

The input/output (I/O) system is the section of a PLC to which all of the field devices are connected. If the CPU can be thought of as the brains of a PLC, then the I/O system can be thought of as the arms and legs. The I/O system is what actually physically carries out the control commands from the program stored in the PLC's memory. The I/O system consists of two main parts:

I. the rack

II. I/O modules

The rack is an enclosure with slots in it that is connected to the CPU. I/O modules are devices with connection terminals to which the field devices are wired. Together, the rack and the I/O modules form the interface between the field devices and the PLC. When set up properly, Each I/O module is both securely wired to its corresponding field devices and securely installed in a slot in the rack. This creates the physical connection between the field equipment and the PLC. In some small PLC's, the rack and the I/O modules come prepackaged as one unit

1.2 Inputs And Outputs

All of the field devices connected to a PLC can be classified in one of two categories:

- I. inputs
- II. outputs

Inputs are devices that supply a signal/data to a PLC. Typical examples of inputs are push buttons, switches, and measurement de-vices. Basically an input device tells the PLC, "Hey, something's happening out here...you need to check this out to see how it affects the control program.

Outputs are devices that await a signal/data from the PLC to perform their control functions. Lights, horns, motors, and valves are all good examples of output devices. These devices stay put, minding their own business, until the PLC says, "You need to turn on now" or "You'd better open up your valve a little more," etc.

There are two basic types of input and output devices:

- I. discrete
- II. analog

Discrete devices are inputs and outputs that have only two states: on and off. As a result, they send/receive simple signals to from a PLC. These signals consist of only 1's and 0's. A 1 means that the device is on and a 0 means that the device is off.

Analog devices are inputs and outputs that can have an infinite number of states. These devices can not only be on and off, but they can also be barely on, almost totally on, not quite off, etc. These devices send receive complex signals to from a PLC. Their communications consist of a variety of signals, not just 1's and 0's. Because different input and output devices send different kinds of signals, they sometimes have a hard time communicating with the PLC. While PLC's are powerful devices, they can't always speak the "language" of every device connected to them. That's where the I/O modules we talked about earlier come in. The modules act as "translators" between the field devices and the PLC. They ensure that the PLC and the field devices all get the information they need in a language that they can understand.

1.3 Control Programs

We talked a little bit earlier about the control program. The control program is a software program in the PLC's memory. It's what puts the control in a programmable controller. The user or the system designer is usually the one who develops the control program. The control program is made up of things called instructions. Instructions are, in essence, little computer codes that make the inputs and outputs do what you want in order to get the result you need. There are all different kinds of instructions and they can make a PLC do just about anything (add and subtract data, time and count events,

compare information, etc.). All you have to do is program the instructions in the proper order and make sure that they are telling the right devices what to do and voila!...you have a PLC-controlled system. And remember, changing the system is a snap. If you want the system to act differently, just change the instructions in the control program. Different PLC's offer different kinds of instructions. That's part of what makes each type of PLC unique.

However, all PLCs use two basic types of instructions:

- I. contacts
- II. coils

Contacts are instructions that refer to the input conditions to the control program that is, to the information supplied by the input field devices. Each contact in the control program monitors a certain field device. The contact waits for the input to do something in particular (e.g., turn on, turn off, etc. this all depends on what type of contact it is). Then, the contact tells the PLC's control program, "The input device just did what it's supposed to do. You'd better check to see if this is supposed to affect any of the output devices."

Coils are instructions that refer to the outputs of the control program that is, to what each particular output device is supposed to do in the system. Like a contact, each coil also monitors a certain field device. However, unlike a contact, which monitors the field device and then tells the PLC what to do, a coil monitors the PLC control program and then tells the field device what to do. It tells the output device, "Hey, the PLC just told me that the switch turned on. That means that you're supposed to turn on now. So let's go!" In PLC talk, this three-step process of monitoring the inputs, executing the PLC control program, and changing the status of the

1.4 How PLC Work?

A PLC works by continually scanning a program. We can think of this scan cycle as consisting of 3 important steps. There are typically more than 3 but we can focus on the important parts and not worry about the others. Typically the others are checking the system and updating the current internal counter and timer values.



Step 1-CHECK INPUT STATUS-First the PLC takes a look at each input to determine if it is on or off. In other words, is the sensor connected to the first input on? How about the second input? How about the third... It records this data into its memory to be used during the next step.

Step 2-EXECUTE PROGRAM-Next the PLC executes your program one in struction at a time. Maybe your program said that if the first input was on then it should turn on the first output. Since it already knows which inputs are on/off from the previous step it will be able to decide whether the first output should be turned on based on the state of the first input. It will store the execution results for use later during the next step.

Step 3-UPDATE OUTPUT STATUS-Finally the PLC updates the status of the outputs. It updates the outputs based on which inputs were on during the first step and the results of executing your program during the second step.

1.5 Why Use PLC's ?

The software advantage provided by programmable controllers is tremendous. In fact, it is one of the most important features of PLCs. Software makes changes in the control system easy and cheap. If you want a device in a PLC system to behave differently or to control a different process element, all you have to do is change the control program. In a traditional system, making this type of change would involve physically changing the wiring between the devices, a costly and time-consuming endeavor. In addition to the

programming flexibility we just mentioned, PLCs offer other advantages over traditional control systems.

These advantages include:

- high reliability
- small space requirements
- computing capabilities
- reduced costs
- ability to withstand harsh environments
- expandability

1.6 Capabilities of the S7-212 CPUs

The S7-200 family includes a wide variety of CPUs. This variety provides a range of features to aid in designing a cost-effective automation solution. Table 2 provides a summary of the major features of each S7-212 CPU.

Table 2

CPU 212 DC power supply, DC inputs, DC outputs

Order Number: 6ES7 212-1AA01-0XB0

General Features		Output Points (continued)			
Physical size (L x W x D)	160 x 80 x 62 mm	Switching delay	25 µs ON, 120 µs OFF		
	(6.3 x 3.15 x 2.44 mL)	Surge current	4 A, 100 ms		
Weight	0.3 kg (0.7 lbs.)	Voltage drop	1.8 V runzimum at maximum		
Power dissipation	5 W at 1.75 A load		current		
User program size/storage	512 words/EEPROM	Optical isolation	500 VAC, 1 min		
User data size/storage	512 words/RAM	Short circuit protection	None		
Data releation	(8 hr minimum at 40° C)	Input Points			
Lecal I/Ol	S inputs/6 ontputs	Input type (IEC 1131-2)	Type I sinking		
Maximum number of expansion modules	2	ON state range	15-30 VDC, 4 mA minimum 35 VDC, 500 ms surge		
Digital I/O supported	64 inputs/64 outputs	ON-state nominal	24 VDC, 7 mA		
Analog 1/O supported	16 inputs/16 outputs	OFF state maximum	5 VDC, 1 niA		
Possiean execution speed	1.2 µsinstruction	Response time 10.0 to 10.7	0,3 ms maximum		
Internal memory bits	128	Optical isolation	500 VAC, 1 min		
Timers	64 timers	Power Supply			
Counters	64 counters	Voltage range	20.4 to 28.8 VDC		
High-speed counters Analog adjustments) software (2 KHz max.)	Input current	60 mA typical, CPU only 500 mA maximum load		
Standards compliance	UL 508 CSA C22.2 142	ULCSA rating	50 VA		
	FM Class I, Division 2 VDE 0160 compliant C'E compliant	Holdup time	10 ms minimum from 24 VDC		
Output Painte	and a standard and a	Innish current	10 A peak at 28.8 VDC		
Cubaut type	Someine transistor	Jusing (non-replaceable)	1 A, 125 V, slow blow		
Voltage range	20.4 VDC to 28.8 VDC	± VDC cuttera	260 mA for CPU 340 mA for expansion 1/0		
Maximum load current Per single point	01040°C 55°C ² 0.75 A 0.50 A	Isolated	No		
Per 2 adjacent points All points total	1.00 A 0.75 A 2.25 A 1.75 A	DC Sensor Supply			
An points total	and the defendence	Voltage range	16.4 to 28.8 VDC		
Single pulse	2A L/R = 10 ms	Ripple/noise (<10MHz)	Same as supplied voltage		
Repetitive	1A L/R = 100 ms 1 W energy dissipation (1/2 LF x switch rate < 1 W)	24 VDC available current Short-circuit current limit	180 mA < 600 mA		
Leakans current	100 BA	Isolated	No		

¹ The CPU reserves 8 process-image input and 8 process-image output image register points for local I/O.

2 Linear detate 40 to 55° C. Vertical mount detate 10° C.



Connector Terminal Identification for CPU 212 DC/DC/DC

CPU 212 AC Power Supply, DC Inputs, Relay Outputs

Order Number: 6ES7 212-1BA01-0XB0

General Features		Input Points	
Decisional size (1 w W x D)	160 x 80 x 62 mm	Input type (IEC 1131-2)	Type 1 sinking
rayacaraty (LAWAD)	(6.3 x 3.15 x 2.44 in.)	ON state range	15-30 VDC, 4 mA minimum 35 VDC, 500 ms surge
Weight	0.4 kg (0.9 lbs.)	and a state provident	24 VDC, 7 mA
Power dissipation	6W	ON state nominat	EVIV: LmA
User program size/storage	512 words/EEPROM	OFF state maximum	2 914., 1 10.9
User data size/storage Data retention	512 words/RAM 50 hr typical	Response time 19.0 to 19.7	0.3 ms maximum
	(8 hr minimum at 40° C)	Optical isolation	500 VAC, 1 min
Local VOI	8 inputs/6 outputs	Power Supply	
Maximum mumber of	2	Voltage/frequency range	85 to 264 VAC at 47 to 63 Ha
Digital I/O supported	64 inputs/64 outputs	Input current	4 VA typical, CPU only 50 VA maximum load
Analog I/O supported	16 inputs/16 outputs	Holdup time	20 ms minimum from 110 VAC
Boolean execution speed	1.2 µs/instruction	Inrush current	20 A peak at 264 VAC
Internal memory bits	128	Fusing (non-replaceable)	2 A, 250 V, slow blow
Timers	e4 nmiers	5 VDC current	260 mA for CPU
Counters	64 counters		340 mA for expansion 1/0
High-speed counters	i softwate (2 KHZ max.)	Isolated	Yes, Transformer, 1500 VA0 1 unio
Analog asperinces	10.508 CSA C22.2.142	DC Sensor Supply	
Standards comprance	FM Class I, Division 2 VDE 0160 compliant CE compliant	Voltage range	20.4 to 28.8 VDC
Choirput Paints		- Ropple noise (< fourite)	180 mA
Output Points	Relay, dry contact	Short circuit current limit	< 600 mA
Voltage range	5 to 30 VDC/250 VAC	Isolated	No
Maximum load current	2 A/point, 6 A/common		
Overcurrent surge	7 A with contacts closed		
Isolation resistance	100 MO minimum (new)		
Switching delay	10 rus maximum		
Lifetime	10,000,000 mechanical 100,000 with rated lead		
Contact resistance	$200 \text{ m}\Omega$ maximum (new)		
Isolation coil to contact contact to contact (between open contacts)	1500 VAC, 1 min 750 VAC, 1 min		
Short ciwarit protection	None		

The CPU reserves 8 process-image input and 8 process-image output image register points for local I/O.





24 VAC CPU 212 Power Supply, DC Inputs, Relay Outputs

der Number: 6ES7 212-1EA01-0XB0

meral Features		inhur a onne	and the first half and
alation (1 x W x D)	160 x 90 x 62 mm	Input type (IEC 1131-2)	Type I sinking
iyacatsize (L'X w X D)	(6.3 x 3.15 x 2.44 in.)	ON state range	15-30 VDC, 4 mA minimum 35 VDC, 500 ms surge
ત્રશ્વોત્રો	0,4 kg (0,9 lbs.)	ON state acminal	24 VDC. 7 mA
timer dissipation	6W	OFF state maximum	5 VDC, 1 mA
ser program size/storage	5.12 words/PEP Joc280	Discounts hittig	
iser data size/storage	512 words/RAM 50 hr typical	10.0 to 10.7	0.3 ms maximum
oata retention	(8 hr minimum at 40° C)	Optical isolation	500 VAC, 1 min
Local VOI	8 inputs/6 outputs	Power Supply	
Maximum number of	2	Voltage/frequency range	20 to 29 VAC at 47 to 63 Hz
Coparsion montes	64 inputs/64 outputs	luput current	4 VA typical, CPU only 50 VA maximum load
Analog I/O supported	16 inputs/16 outputs	Holdup time	20 ms minimum from
Boolean execution speed	3.2 µsinstruction		24 VAU
Internal memory bits	128	Innish current	2.0 A 250 V slow blow
Timets	64 timets	Fusing (non-replacease)	260 mA for CPU
Counters	64 counters	3 VDC current	340 mA for expansion I/O
High-speed counters	1 software (2 KHz max.)	Isolated	Yes, Transformer, 500 VA
Analog adjustments	1		1 11310
Standards compliance	11L 508 CSA C22.2 142 TALCINES Division 2	DC Sensor Supply	and the second second
	VDE 0160 compliant CE compliant	Voltage range	1 V peak-to-peak maximu
Output Paints		24 VDC available current	180 mA
Cutrui MDE	Relay, dry contact	Short circuit current limit	< 600 mA
Voltage range	5 to 30 VDC/250 VAC	Isolated	No
Maximum load current	2 A /point, 6 A /common		
Overcurrent surge	7 A with contacts closed		
Isolation resistance	100 MQ minimum (new)		
Switching delay	10 ms maximum		
Lifetime	10,000,000 mechanical 100,000 with rated load		
Contact resistance	200 mQ maximum (new)		
Isolation coil to contact contact to contact (between open contacts)	1500 VAC, 1 min 750 VAC, 1 min		
thest simult protection	None		

1 The CPU reserves & process-image input and 8 process-image output image register points for local 1/0.



Connector Terminal Identification for CPU 212 24 VAC/DC/Relay

LT SIMATIC S7-200 Quick Reference Card

Internet in the second		Priority in Group		
and the second sec	8	Porto: Receive character	DEDI	0
		Portô: Transmit	and and a	0
maniation	23	Porto: Receive message	DE VE	9
array do	24	Port 1: Receive message	墨	1
alleren batota?,	25	Past 1: Receive character	(H)	1
	26	Port 1: Transmit complete	3	1
		Rising edge, 19.0"	maina	0
	2	Rising edge, 19.1	121 101	1
	4	Rising edge, 19.2	TIGI E	2
	6	Rising edge: M.3		3
	1	Faling etge, 10.0*	DIDIDO	4
	3	Faling edge, E.1	11.02 M	\$
	6	Faling edge, 10.2	য়া এ প	6
	7	Faling edge, 10.3	a al M	7
in merupit	12	HSC0 = piesel value*	20.01.01.01	0
puony	13	HSC1 = preset value	H DI H	8
	14	HSC1 direction charge	10100100	
	15	HSC1 external reset	2122.32	10
	16	HSC2 = preset value	团团团	11
	17	HSC2 dection change	四國國	12
	18	HSC2 external reset	DI OR IN	13
	19	PLSO	田田道	14
	20	PLS1	四日王	15
	10	Timed0	ole ole	0
Timed interrupts	11	Timed 1	KI DI M	1
Lourest priority	21	132 = preset	0194	2
	22	190 = preset	ELEI	3

SIMATIC S7-200 Quick Reference Card

Special Memory Bits						
SMD A	Always On	SM1.0	Result of operation = 0			
5140.1	First Scan	SM1.1	Overflow or Negal value			
5102	Retention data bas	8412	Negativo result			
SIN	Powerup	SM13	Division by 0			
ST TO d	30 sol / 30 son	SM1.4	Table kdi			
10.5	0.5 soll / 0.5 son	SM15	Table erapty			
51.0.6	Off Iscan/on Iscan	SI-11.6	BED to binary conversion error			
51107	Switch in RUN position	SM1.7	ASC I to her conversion error			

	H	ligh-Speed	CounterN	lodes		
	Counter			Inpu	his.	
HSCO	Maximum 2 kHz	य अञ्चय	10.8			
HSC1	T WHZ I	29 kHz 2030	10.6	10.T	11.8	$\Gamma_{k} = I_{1}$
HBC2	7 H-Iz III	20 kHz gill	11.2	T1.8	11.4	I1.8
Mode	Description Single phase with internal		Ck	ock	Reset	Start
0102			Up/Down: 0, 1, 2		1.2	2
305	Single phase with esternal direction		Up/Down: 3, 4, 5	Direction 3, 4, 6	4,5	5
Gob	Two phono		Up: 6.7,8	Bonn: 6, 7, 8	7,8	R
91011	11 Qualitatum AP		A: 5, 10, 11	B: 9. 10, 11	10, 11	11
TT CP	212 21 C	PU214 III (PU 215 1	CPU 216		

	Ran	o Limit			Accessi	bla 35	
212	214	215	216	Bit	Byte	Word	DWord
612 W	2048 W	4095 W	4095 W				
512 W	2048 W	2500 W	2560 W				
0 12 11	0.4895	0.5119	0.5110	Viry	VBbr	VNx	MD*
6.7	0.7	0.7	0.7	bay	IBx	HV/x	Dx
16.7	0.7	0.7	0.7	Oncy	OB.	Q Wix	QDa
0.0	0.10	0.30	0.30			AllVa	
0-30	0.30	0.90	0.30	1		ACM's	
0.30	11.10	10.94	6.31	Likey	MBs	MWW	MOs
0.15	0.0	5 104	0.191	Shby	SMS	ShiWa	SMDx
0.46	0.85	10104	680	14		1x	
Ø	D,64	9/04	14.5.02	Te	-	Tx	1
1.4	1-4, 65-58	1-4, 65-68	1-4, 00-00 7 04 00 0F	The second secon	-	Ta	-
6-31	5-31, 09-95	5-31, 69-95	5-31,000 00	T-		Tx	-
39	32,96	32, 96	32, 96	To	-	Tr	-
33.36	33.36, 97-100	53.36, 97-100	33-36, 97-100	11	-	Tr	-
37-63	37-63, 101-127	37-63, 101-255	37.63, 101.255	14	-	- 67	
0.63	0-127	0.255	0.255	ta:		6.4	105
Ð	5.2	0.2	0.2			100	Are
0.3	0.3	0.3	03		ALX	PLA	100.0
0.7	0.15	0.31	0.31	Say	246x	Silva	atv
6.63	0.255	D-255	0.255				
0.15	0.63	0.63	D-1-3				
0.04	0.127	0.127	0-127	1			
01810 13	0.29	0.23	0.26				
1. 1. a. a. 1.	NPA	0.7	0.7	1			
NA D. 14	Diet B.	Port # . DP Port	Port 9, Port 1	1			
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Boolean	Inst	ructions
	Lone	1
AL 14	Line	investinie
	Lon	Not
	Lon	a Mai Inningstanie
	ANI) krome kate
	APRIL APRIL	Not
	ANI	0 Not insuedinte
	OR	
	OR	hamediate
H	OR	Hot
н н	OR	Hit Issuelate
H1 H2		
- H1, H2	L III	al result of Byte Company (=, >=, or <=) N2
N1, H2		
🗰 H1, H5	AN	Described Date Constant
H1, H2	NI	t=, >=, or <=) ₩2
H1, H2	-	
H1, H-	i ce	areads of Byte Company
- H1, H2	N	(=, >=, or <=) N2
= H1, H	+	
H1, H2	Lo	and romat of Word Company-
H1. H2	N	(=, >=, or <=) ₩2
111, 11	+	
H1, H2	A	ND result of Word Company
H1. N2	N	(=, >=, pr <=) Hz
HI H2	+	
H1, 112	0	Remail of Word Company
CANN'S 111, 102	1	the seat of section
100 H1, H2		
100= H1, H2	N	tanti renami of Dynord Company 1 (a, >=, or <=) N2
LDC= H1, H2		
AL H1, H2		MD
AD = 111, HF	i.	It (≈, ≥≈, or <≈) N2
AD-= H1, H2	-	
DC= H1, H2	1	R made of DWord Company
Deci= H1, H2	1	11 (=, >=, or <=) H2
ODK= H1, H2	-	
	1	and result of Real Company
IDR H1.H2	1	vit je, ze, or sey na
AR: 111,112	1	
AR= H1. H2	10	AND result of Real Company-
AR= 11.12	a.	differentiate from
-OR= N1, H2	T	in the street
0R= H1, H2	11	NT (=, >=, or <=) H2
UR<= 111, 112	25	
NDY		Stack Megalion
tu	T	Detection of Rising Lidge
ID		Detection of Falling Edge
= H		Assign Value
=t H		Ansign Value Instructings
S B.BILN		Set of Hereip
R S_BIT, N		House on Hange
BI S.BILN		Read bit Ranae trame date
Hath Inco	1170	t and Decrement
idout, mete	nstr	uctions
+1 NIL OUT		
D IN OUT		Acid Baleger, 17/2 ord or Real
+R INI, OUT	32	NUCOTON
-I INI, DUT		Subtract Integer, DWard, or
-D INI, OUT		Fibal
-R INLOUT	111	OUT-NEOUT
M.A. INI, OUT	-	Multiply Interpet or Real
R IN, OUT	20	NI 1 OUT = OUT
DN INI, OUT		Divide Integer or Real
R INI, OUT	14	OUT / INI = OUT
the second se		

SCIRT IN, OUT OF	Signare Root
NCE OUT #	Incompany Date, (Court or
NOW OUT	Increment Byte, word or
NCD OUT	
DECB OUT	
DECW OUT	Destorment Byte, Word, or
	Difficient
	DID Loop
PD falle Loop II	
Timer and Cou	ner instructions
TON TRA, PT	Cin Delay Timer
TONR Two PT	Reteritive On Dolay Timer
CIU Cars FV	Gount Up
CRID Care PV	Gount Up/Down
Past time the	ock Instructions
NUM THIN CH	the state of the state
TOOR T a	Resident filler of they can be
TODW T	These time of Day Hock
Program Cor	trol Instructions
END	Conditional End of Program
MEND	Main Program Lad of Program
100	Transition to STOP Made
3100	Wet (Dog Regel (100 and
NDR	and the prost the stat
JIMP N	Jump to defined Labol
LBL N	Define a Label to Jump ID
CALL N	Call a Subroutine
SER N	Define a Subioutine to be
CRET	Latiod
RET	Conditional Festurn from auto
	Unsueditional Return from
	SER
FOR Index Initial,	E-H-H-con
ARVE -	Les nim rook
NEAT III	
LSCR N	Load, Transition, and End
SCRT N	Sequence control reary
SCRE	
Move. Shift. Rota	tu, and Fill Instructions
MOVE IN, OUT	
HOWY IN, OUT	11
MOND IN OUT	BIDVE BYES, HERG, LYNNIN, PUM
MONTE IN OUT	
TRANS INCOMENTIN	
CLASS INCOLT SI	Ele k Nove Dyte, Word
	DWord
ESTILO UN, CHOT, IT	
SWAP IN	Swap Bytes
SHRB Dula, 5_bit, N	Shilt Register Bit
SRB OUT, N =	1
SRW OUT, N	Shill Right Byte, Word, Difford
SRD OULN	
SIR OUT N	1
CALIN CHART AL	Shit Let Ret Word Dillord
ELST OUT N	water and a part of some second
SLD OUT N	
RRB OUT, N	Battes Right Bide Word.
RRW OUT, N	DWord
RED OUT, N	
RLB OUT, N	4
RUW OUT N	Rotate Left Dyte, Word, D'Non
RLD OUT N	
CB1 IN OUT N	Fill memory space with pattern
CILL IN, DUT, N	in Operation
LOG	La the entire free
1 41 15	And for compensions
ALD	Of Icr combinations
CLD	The same starts as the
CLD	Logic Push (stack control)
LPS	Logic Push (stack control)
LPS LPS LPP	Logic Push (stack control) Logic Read stack control Logic Pop Long Logic Pop
LPS LPP LPP	Logic Push (stack control) Logic Pop (stack control) Logic Pop (stack control)
ALD CLD LPS LRD LPP ANCB IN1, CUT	Logic Push (stack control) Logic Pop (stack control) Logic Pop (stack control) 20 Logical And of Byte, Work, ar
ALD LPS LRD LPP ANDS IN1, OUT ANDW IN1, OUT	Logic Push (stark control) Logic Read (stark control) Logic Pop I and Control Logic And of Byte Went, or DWord
ALD LPS LRD LPP ANDB IN1, OUT ANDW IN1, OUT ANDD IN1, OUT	Logic Push (start: control) Logic Read (start: control) Logic Pop (start control) Logic Pop (start control) Logic Pop (start control)
ALD LPS LRD LPP ANDS IN1, OUT ANDW IN1, OUT ANDD IN1, OUT	Logic Push (statck control) Logic Read statck control Logic Rep (statck control) Logic Rep (statck control) Logical And of Byte, Went, an DWiced
ALD CLD LPS LPS LPP ANDS IN1, OUT AND/V IN1, OUT AND/ IN1, OUT CRS IN1, OUT CRS IN1, OUT	Logic Push (state): control Logic Read (state): control Logic Pop (state): control Logical And of Byte, Word, and Differed
ALD CLD LPS LRD LPP ANDS IN1, OUT ANDW IN1, OUT ANDD IN1, OUT CRD IN1, OUT CRD IN1, OUT	Logic Push (start: control) Logic Read (start: control) Logic Pop (start: control) Logical Anci of Byte, Werd, an DWood Logical Cr of Byte, Word, and DWord

CHar PH, OUT	and
Difford	
CRD INLOUT	
NVB OUT EI Invent Dyn, Word and DWo	nd
INW OUT (T's complement)	
N/D OUT	
Table, Find, and Conversion Instruction	
ATT Dista, Table III Add status to table	
LIFO Table Data III Get data from table	
FIFC Table, Data 💷	
FND-Sar Paten, Inde 🔟	
FND Ser, Paten, Inde III First data value in table the	st i
FND Scr. Pains inde III matches companyou	
FND> Sar, Patro, lack (11)	
BCDL OUT General BCD to brimper	1
IDCD CUT Convertinger to PCD	
DIR N. OUT I Convert DWheel to Real	
TRUNC N. OUT III Convent Resulto DWord	
ATH N, OUT, LEN Commit ASCIED HEX	
HTA N. OUT LEN Convert HEX to ASCH	
DECO N, OUT Descale	
ENGO N. OUT Excede	
SEG N. OUT Generale 7-segment part	-10
Interrupt	
intr M Heninging of Interrupt real	Áne-
cantinenal Restore form	2
Indersupt	
Renan Iran Interrupt	
ENI Enable Interrupts	
Deable Interrupts	
ATCH BIT EXCELLE Attach Interrupt routine to	0
DICH ENERT OVER	
Dich Event	
Communication	
XMT TABLE PORT	
DATA TABLE.	
PORT II Perpet lecone riteren	-
NETR TABLEPORT II Network Read	
NETW TABLE, PORT DI Network Wiles	
High Spend Instructions	
HIXEF HSG. Moder Define High Speed Cou	nley
nacibe	
HSC N Activate High Speed Co	UNICI
PLS X III Pulse Durput	
Instructions are valid for the individu S7-200 PLCs as marked according to following key: 214. 215, and 216 only 215 and 216 only If not marked, the instructions are ve for all S7-200 PLCs.	al the alid

2. ELECTRONIC CIRCUIT DEVICES

2.1.DIODE

2.1.1.PN Junction



Figure 2.1 Basic pn structure at the instant of junction formation. Both majority and minoriy carriers are shown.

Figure 2.1(a) shows a pn junction formed between the two regions when a piece of silicon is doped so that half is n-type and the other half is p-type. This basic structure forms a semiconductor diode. The n region has many free electrons (majority carriers) and only a few thermally generated holes (minority carriers). The p region has many holes (majority carriers) and only a few thermally generated free electrons (minority carriers). This is shown in Figure 2.1(b). The pn junction is fundamental to the operation of diodes, transistors, and other solid state devices .

2.1.2. Forward Bias

The term bias in electronics refers to a fixed dc voltage that sets the operating conditions for a semiconductor device. Forward bias is the condition that permits current across a pn junction. Figure 2.2 shows a dc voltage connected in a direction to forward-bias the diode. Notice that the negative terminal of the battery is connected to n region (called cathode), and the positive terminal is connected to the p region (called the anode).



Figure 2.2 Forward-bias connection. The purpose of the resistor is to limit the current prevent damage to the diode.

This is how forward bias works: The negative terminal of the battery pushes the conduction electrons in the n region toward the junction, while the positive terminal pushes the holes in the p region also toward the junction. (Recall that like charges repel each other.) When it overcomes the barrier potential, the external bias voltage source provides the n-region electrons with enough energy to penetrate the depletion layer and cross the junction, where they combine with the p-region holes. As electrons leave the n-region, more folw in from the negative terminal of the battery. So, current through the n-region is the movement of the conduction electrons (majority carriers) toward the junction.

When the conduction electrons enter the p region and combine with holes, they become valence electrons. They then move as valence electrons from hole to hole toward the positive anode connection. The movement of these valence electrons essentially creates a movement of holes in the opposite direction as we our learned earlier. So, current in the p region is the movement of holes (majority carriers) toward the junction. Figure 2.3 illustrated electron flow in a forward-biased diode.



Figure 2.3 Electron flow in a pn junction diode.

2.1.3.Reverse Bias

Reverse bias is the condition that pervents cuurent across the pn junction. Figure 2.4. shows a dc voltage source connected to reverse-bias the diode. Notice that the negative terminal of the battery is connected to the p region, and the positive terminal is connected to the n region. The negative terminal of the battery attracts holes in the p region away from the pn junction, wihle the positive terminal also attracts electrons away from the junction. As electrons and holes move away from the junction, the depletion layer widens; more positive ions are created in the n region, and more negative ions are created in the p region, as shown in Figure 2.5.



Figure 2.4 Reverse bias connection.

deplation layer widens until the potential difference across it equals the external voltage. At this point, the holes and electrons stop moving away from the junction majority current ceases, as indicated in Figure 2.5(b). The initial movement of ajority carriers away from the junction is called transient current and last only for a voltage short time upon application of reverse bias.



Figure 2.5 Reverse bias.

When the diode is reverse-biased, the depletion layer effectively acts as an insulator between the layers of oppositely charged ions. This effectively forms a capacitor, is illustrated in Figure 2.5(c). Since the deplation layer widens with increased reverse-biased voltage, the capacitance decreases and vice versa. This internal capacitance is called deplation-layer capacitance.

2.1.4.Diode Characteristic Curve

A diode conducts current when it is forward-biased if the bias voltage exceeds the barrier potential, and the diode prevents current when it is reverse-biased at less than the

The upper right quadrant of the graph represents the ard-biased condition. As we can see, there is essentially no forward current (If) for tward voltages (Vf) below the barrier potential. As the forward voltage approaches the barrier potential (typically 0.7V for the silicon and the 0.3V for germanium), the current begins to increase. Once the forward voltage reaches the barrier potential, the current insreaeses drastically and must be limited by a series resistor. The oltage across the forward-biased diode remains approximately equal to the barrier potential but increases slightly with forward current.

The tower left quadrant of the graph represents the reverse-biased condition. As the reverse voltage (V_R) increases to the left, the current remains near zero until the breakdown voltage (V_{BR}) is reached. When breakdown occurs, there is a large reverse current which, if not limited, can destroy the diode. Typically, the breakdown voltage is greater than 50V for most rectifier diodes. Rectifier diodes should not be operated in reverse breakdown.



Figure 2.6 Diode characteristic curve

115 Diode Symbol

Foure 2.7(a) is the standart symbol for a general-purpose diode. The arrow points in the frection of conventional current. The two terminals of the diode are the anode and enhode. When the anode is positive with respect to the cathode, the diode is forward based and current is from anode to cathode, as shown in Figure 2.7(b). If there is any cuestion about terminal polarities, always check the manufacturer's data book. Remember that when the diode is forward-biased, the barrier potential V_B always appears between anode and cathode, as indicated in the figure. When the anode is negative with respect to the cathode, the diode is reverse-biased, as shown in Figure 2.7(c). The bias battery voltage is designated V_{BB} and is not the same as the barrier potential.



Figure 2.7 Gneral purpose diode and conditions of forward and reverse bias. The resistor limits the forward current to a safe value.

2.2.BİPOLAR JUNCTION TRANSISTORS

2.2.1.Introduction

The transistor was invested by a team of three men at Bell Laboraturies in 1947. Although this first transistor was not bipolar junction device, it was the begining of a technological revolution that is still continuing. All of the complex electronic devices and systems today are an outgrowth of early developments in semiconductor transistors. There are two basic types of transistors the bipolar junction transistor (BJT), and the field effect transistor (FET). The BJT is used in two broad areas as a linear amplifier to boost or amplify an electrical signal and as an electronic switch.

2.2.2.Transistor Construction

The bipolar junction transistor (BJT) is constructed with three doped semiconductor regions seperated by two pn junctions. The three regions are called **emitter**, **base**, and **collector**. The two types of bipolar transistor are shown in Figure 2.8. One type consists of two n regions seperated by n region (pnp).



Figure 2.8. Basic bipolar transistor construction.

The pn junction joining the base region and the emitter region is called the base-emitter junction. The junction joining the base region and the collector region is called base-collector junction, as indicated in Figure 2.8(a). A wire lead connects to each of the three regions, as shown. These leads are labeled E, B, and C for emitter, base, and collector, respectively.

The base region is lightly doped and very narrow compared to the heavily doped emitter and collector regions. Figure 2.9 shows the shematic symbols for the npn and pnp transistors. The term bipolar refers to the use of both holes and electrons as



Figure 2.9. Standard bipolar junction transistor (BJT) symbols.

2.2.3.Basic Transistor Operation

Figure 2.10 shows the proper bias arrangement for both npn and pnp transistors. Notice that in both cases the base-emitter (BE) junction is forward-biased and the collector (BC) junction is reverse-biased.



Figure 2.10. Forward-reverse bias of a bipolar transistor.

Now, let's examine what happens inside the transistor when it is forward-reverse biased. The forward bias from base emitter narrows the BE depletion layer, and the reverse bias from the base- collector widens the BC depletion layer, as depicted in Figure 2.11(a). The n type emitter region is teeming with conduction-band (free) electrons that easily diffuse across the forward-biased BE juntion in to the p type base region, just as in a forward-biased diode. The base region is lightly doped and very

electrons flowing across the BE junction can combine with the available holes. These relatively few recombined electrons flow out of the base lead as valence electrons, forming the small base current I_B, as shown in Figure 2.11(b).

Most of electrons flowing from the emitter into the narrow base region do not recombine and diffuse into the BC depletion layer. Once in this layer they are pulled across the reverse-biased BC juntion by the depletion layer field set up by the force of attraction between the positive and negative ions. Actually, we can think of the electrons are being pulled across the reverse-biased BC junction by the attraction of the positive ions on the other side. This is illustrated in Figure 2.11(c). The electrons now move through the collector region, out through the collector lead, and into the positive terminal of the external dc source. This forms the collector current, Ic, as shown. The amount of collector current depends directly on the amount of base current and is essentially independent the dc collector voltage.



Figure 2.11. Illustration of BJT action. The base region is very narrow, but it is shown wider here for clarity.

2.3.SYNCHRONOUS UP/DOWN COUNTERS ICs

Four-bit synchronous binary counters are available in a single integreted-circuit (IC) package. The popular synchronous IC counters are the 74192 and 74193. They both have some features that were not available on the ripple counter ICs. The can count up or down and can be preset to any count that we desire. The 74192 is a BCD decade

sed for both counters is shown in Figure 2.12.



Figure 2.12 Logic symbol for the 74192 and 74193 synchronous counter ICs.

There are two separate clock inputs: C_{pU} for counting up and C_{pD} for counting down. One colck must be held HIGH while counting with the other. The binary output is taken from Q₀ to Q₃, which are the outputs from four internal J-K flip-flops. The Master Reset (MR) is an active-HIGH Reset for resetting the Q outputs to zero.

The counter can be preset by placing any binary value on the parallel data inputs (D₀ to D₃) and then driving the Prallel Load (\overline{PL}) line LOW. The parallel load operation will change the counter outputs regardless of the conditions of the clock inputs.

The Terminal Count Up $(\overline{TC_U})$ and Terminal Count Down $(\overline{TC_D})$ are normally HIGH. The $\overline{TC_U}$ is used to indicate that the maximum count is reached and the count is about to recycle to zero (carry condition). The $\overline{TC_U}$ line goes LOW for the 74193 when the count reaches 15 and the clock (CPU) goes HIGH to LOW. TCU remains LOW until C_{PU} returns HIGH. This LOW pulse at $\overline{TC_U}$ can be used as a clock input to the next-higherorder stage of a multistage counter.

The $\overline{TC_{U}}$ output for the 74192 is similar except that is goes LOW at 9 and a LOW C_{pU} . The Boolean equations for $\overline{TC_{U}}$, therefore, are as follows:

LOW at $\overline{TC_U} = Q_0 Q_1 Q_2 Q_3 \overline{CpU}$ (74193)

LOW at $\overline{TC_U} = Q_0 Q_3 \overline{CpU}$ (74192)

Terminal Count Down ($\overline{TC_D}$) is used to indicate that the minimum count is reached and the count is about the recycle to the maximum (15 to 9) count (borrow condition). Therefore, $\overline{TC_D}$ goes LOW when the down-count reaches zero and the input clock (C_{PD}) area LOW. The Boolen Equation at $\overline{TC_D}$ is

LOW at $\overline{TC_D} = \overline{Q_0} \ \overline{Q_1} \ \overline{Q_2} \ \overline{Q_3} \ \overline{CpD}$ (74192 and 74193)

The function table shown in Table 2.1 can be used to show the four operating modes (Reset, Load, Count Up, and Count Down) of the 74192 / 74193

Operating mode	Inputs								Outputs					
	MR	PT	CpU	CpD	Do	<i>D</i> ₁	D 2	D ₃	0.	<i>Q</i> ₁	Q 2	Q 3	TCu	TC
Reset	Н	××	×××	L	××	××	××	××	L	L	L L	L	H H	L H
Parallel Load			××L	L H ×	L L H	L L H	L L H	L L H H	L L H	L H H	L H H	L H H	H H L H	L H H H
Count Up Count Down	L	H	1 H	H 1	××	××	××	× ×	Count up Count down				H H	H H

Table 2.1 Function Table for the 74192 / 74193 Synchronous Counter Ics.

• H = HIGH voltage level; L = LOW voltage level; × = don't care; [= LOW-to-HIGH clock transition

2.4.NOT GATE (INVERTER)

The inverter is used to complement or invert a digital signal. It has a single input and single output. If HIGH level (1) comes in, it produces a LOW level (0) output. If a LOW level (0) comes in , it produces a HIGH level (1) output. The



Figure 2.13. Inverter symbol and truth table.

symbol and truth table for the inverter gate are shown in Figure 2.13.

The operation of the inverter is very simple and can be illustrated further by studying the timing diagram of Figure 2.14. The timing diagram graphically show us the operation of the inverter. When the input is HIGH, the output is LOW, and when the input is LOW, the output is HIGH. The output wave form is therefore the exact complement of the input.



Figure 2.14. Timing analysis of an inverter gate.

The Boolen equation for an inverter is written $X = \overline{A}$ (X = NOT A). The bar overthe A is an inversion bar, used to signify the complement.

2.5. D TYPE FLIP-FLOP (Data flip-flop)



Figure 2.15. S and R input and output relation for D flip flop.

Can be formed from the gated S-R flip-flop by the adddition of an inverter. In Figure **16** we can see that S and R will be complements of each other, and S is connected to a **see** line labeled D (Data). The operation is such that Q will be the same as D, while G **HIGH** and Q will remain "latched" in whatever state it was in before the HIGH-to-LOW transition on G.



Figure 2.16. Gated D flip flop.

2.6.OPTOCOUPLERS



Figure 2.17. An optocoupler consists of an LED packaged with a photodiode or phototransistor

An optocoupler is a light-activated electronic switch. It consists of a light-emitting diode (LED) packaged with a *photodiode* or *phototransistor*, devices that are activated (turned on) by lighting energy. See Figure 2.17. A pulse applied to the input side turns on (illuminates) the LED, and the light energy it generates activated photodiode or phototransistor. The latter devices can be connected to an open circuit to perform switching functions in any of the applications for which conventional diodes and transistors are used. The principal use of optocouplers is to interface circuits where good electrical isolation is required. Since there is no physical contact between the input

circuit and output circuit, each can have a seperate ground, or referance. Because of this ability to isolate circuits, optocouplers are also called optoisolators.

The output circuit in Figure 2.17 contains phototransistors. In some commercially available units, the base is not an externally accessible terminal, since the only collector and emitter are neccessay to serve as switch terminals. In other units, the base terminal is accessible so that the user can have optionally connect the output circuit between the base and collector. In this mode, the device serves as a photodiode rather than as a phototransistor. The advantage of the photodiode mode is that switching is much faster than phototransistor mode. The advantage of the phototransistor mode is that, as in conventional devices, the transistor has the capability of driving a load.

The current tansfer ratio (CTR) of an optocoupler is the ratio of output current to input current. Depending on device design and application, it may range from 0.1 or less to several hundred. Optocoupler specifications usually include electrical isolation, expressed as a voltage. This voltage is the input-output voltage that the device can withstand without electrical cunduction occuring between input and output. A typical value is 2kV. Other important specifications of an optocoupler relate to switching speed. These may be quoted in terms of rise and fall times. Typical value are 1 microsecond for an optocoupler using a photodiode and 5 microseconds for an optocoupler using a phototransistor.

2.7. INTERFACING RELAYS AND SOLENOIDS

A relay is mechanical switch or set of switches that are pened or closed by a magnetic field generated when electrical current is passed through a coil. See Figure 2.18. In the context of a relay, the switches are called contacts. When no current passes through the coil, it is said to be deenergized, the contacts are in their "normal" state: normally open or normally closed. When the coil is energized, the contacts switch to the opposite state. Like optocouplers, relays provide electrical isolation between an input circuit (the coil) and output circuits, the circuits connected to the contact. They are used to drive heavy loads. A relatively small voltage applied to the coil circuit opens and closes heavy-duty contacts that can switch high voltages and currents. A very common application of relay is to start oand stop and electrical motor. A solenoid is similar to a relay


Figure 2.18. The electromechanical relay.

except in stead of opening and closing switches when its coil energized, it opens or closes a mechanical value. Solenoids are used the control flow of liquits and gases. Relays and solenoids are both very slow in comparison to electronic switching speeds, so they are used only when the load is to be switched in or out of a circuit for long intervals of time. An example of such a load is the fan motor in an air conditioning system.

Figure 2.19 shows a circuit used to drive a relay coil. One of the problems with driving a relay is that a very large voltage spike appears across the coil terminals.



Figure 2.19. A relay-driver cicuit.

2.8. 555 TIMER

2.8.1.Introduction

The 555 Timer is a TTL digital logic circuit that is used in the controller circuit to produce a periodic square wave signal. The period and duty cycle of the square wave signal are determined by the resistors and capacitors connected to the timer. A square wave with a 50% duty cycle is desired. In order to obtain exactly a 50% duty cycle from the 555 Timer, two resistors of identical value are required. Since it is impractical to obtain two resistors of identical value, two resistors close in value are used to generate a square wave with a duty cycle close to 50%, and then a JK flip flop is used to create a produced by the JK flip flop is 1/2 the frequency of the output of the 555 timer.

2.8.2. Time Delay Circuit

555 IC is used for monostable and also for astable. For astable and monostable the time constant can be adjusted between microseconds and a few hours. Since it works with 5V and 18V we can adopted to all type of circuits. An also it feeds 200mA, bulbs, relays, and some components which are like bulbs and relays can be drived directly. When the output of IC is high the IC spends 10mA by itself, and when the output reaches the zero volt it uses 1mA of 200mA.

In my circuit it is used as monostable oscillator.

2.9. DEMULTIPLEXERS

Demultiplexing is the opposite procedure from multiplexing. We can think of demultiplexer as a data distributor. It takes a single input data value and routes it to one of several outputs, as illustrated in Figure 2.20.



Figure 2.20. Functional diagram of a four-line demultiplexer.

Integrated-circuit demultiplexers come in several configurations of inputs/outputs. There are two types which is one of the 74139 dual four-line demultiplexer and other one is 74154 16-line demultiplexer.

The logig diagram and logic symbol for the 74139 are given in Figure 2.21. Notice that the 74139 is divided into two equal sections. By looking at the logic diagram, we will see that the schematic is the same as that of a 2-line-to-4-line decoder. Decoders and demultiplexers are the same, except with a decoder we hold the E enable line LOW and enter a code at the A₀A₁ inputs. As a demultiplexer, the A₀A₁ inputs are used to select the destination of input data. The input data are brought in via the E line. The 74138 3-line-to-8-line decoder.



Figure 2.21. The 74139 dual 4-line demultiplexer: (a) logic symbol; (b) logic diagram.

To use the 74139 as a demultiplexer to route some input data signal to, let's say, the 2a output, the connections shown in Figure 2.22 would be made. In the figure the destination 2a selected by making $A_{1a} = 1$, $A_{0a} = 0$. The input signal is brought into the enable line (E_a). When E_a goes LOW the selected output line goes LOW; when E_a goes high, the selected output line goes HIGH.



Figure 2.22. Connections to route an input data signal to the 2_a output of a 74139 demultiplexer.



Figure 2.23. The 74154 demultiplexer connections to route an input signal to the 5 output.

The 74154 can also be used as a 16-line demultiplexer. Figure 2.23 shows how it can be connected to route an input data signal to the 5 output.

2.10. CODE CONVERTER

Quite often it is important to convert a coded number info another from that is more usable by a computer or digital system. The prime example of this is with binary-codeddecimal (BCD). We have seen that BCD is very important for visual display communication between a computer and human begins. But BCD is very difficult to deal with arithmetically. Algorithms, or procedures, have been developed for conversion of BCD to binary by computer programs (software) so that the computer will be able to perform all arithmetic operations in binary. Another way to convert BCD to binary, the hardware approach, is with MSI integrated circuits. Additional circuitry is involved, but it is faster to convert using hardware rather than software.

3.OPERATION PRINCIPLE OF CIRCUIT

3.1. GENERAL OPERATION OF TELEREMOTE CIRCUIT



Figure 3.1. Receiver circuit



Figure 3.2. Counter circuit.



Figure 3.3. Time delay circuit.



Figure 3.4. Control circuit.



Figure 3.5. Oscillator Circuit

When the DTMF is send to the optocoupler part of the circuit the light emitting diode will emitte lights. The light emitted will be detected by the phototransistor will convert the light source to an electrical signal the TR1 will be driven and then the coil of the relay will be magnetized. Since the signal of the telephone line is high for a certain time and then of therefore when the high signal comes to the circuit the relay will operate but when low signal comes to the circuit the relay will not operate. This on and off period will be detected by counter part of that circuit. Each active position of relay will be accepted as one by counter circuit. And counter will count up to eight. When the eight tones are reached. The telephone you are calling will answer you. And after this operations the timer will set eleven seconds time delay. This time delay can be adjusted by changing the value of the capacitors and resistors. And also the counter value can be changed between some specific values of the resistors and capacitors are shown in Table 3.1.

	0.001µF	0.01µF	0.1µF	1µF	10µF	100µF	1000µF
11-0	0.001	1148	110µS	1.1mS	11mS	110mS	1.1S
1.01-0	1148	110uS	1.1mS	11mS	110mS	1.18	115
1001-0	11005	1 lmS	11mS	110mS	1.18	115	1105
100852	1 1 1 mS	11mS	110mS	1.15	118	1108	1100S
$1M\Omega$	1.1mS	11110	TIOME				

Table 3.1 Resistors and capacitors value of monostable timer.

This eleven seconds time will let you do your operation. In this stituation, operations shoul be finished in limited time which is eleven seconds. When the zero button is pressed after operation, the operation will be finished. Or after counter counts eight if you zero button is pressed the system will give you unlimited time to perform your operation and again by pressing zero button, the operation will be finished.

3.2. OPERATIN OF THE CONTROL CIRCUIT

The circuit uses IC MT8870 (DTMF to BCD converter), 74154 (4-to-16-line Demultiplexer), and five CD4013 (D flip flop) ICs. The working of the circuit is as follows.

Once a call is established (after hearing ring-back tone), dial "0" in DTMF mode. IC1 decodes this as '1010', which is further demultiplexed by IC2 as output 010 (at pin 11) of IC2 (74154). The active low output of IC2, after inversion by an inverter gate of IC3 (*CD4049*), becomes logic 1. This is used to toggle flip-flop-1 (F/F-1) and relay RL1 is energised. Relay RL1 has two changeover contacts, RL1(a) and RL1(b). The energised RL1(a) contacts provide a 220-ohm loop across the telephone line while RL1(b) contacts inject a 10kHz tone on the line, which indicates to the caller that appliance mode has been selected. The 220-ohm loop on telephone line disconnects the ringer from the telephone line in the exchange. The line is now connected for appliance mode of operation.

"O' is not dialed (in DTMF) after establishing the call, the ring continues and the enhone can be used for normal conversation. After selection of the appliance mode of peration, if digit '1' is dialed, it is decoded by IC1 and its output is '0001'. This BCD de is then multiplexed by 4-to-16-line demultiplexer IC2 whose corresponding tput, after inversion by a CD4049 inverter gate, goes to logic 1 state. This pulse gles the corresponding flip-flop to alternate state. The flip-flop output is used to trive a relay (RL2) which can switch on or switch off the appliance connected through its contacts. By dialing other digits in a similar way, other appliances can also be switched 'on' or 'off'. Once the switching operation is over, the 220-ohm loop resistance and 10kHz tone needs to be removed from the telephone line. To achieve this, digit '0' (in DTMF mode) is dialed again to toggle flip-flop-1 to de-energise relay RL1, which terminates the loop on line and the 10kHz tone is also disconnected. The telephone line is thus again set free to receive normal calls. This circuit is to be connected in parallel to the telephone instrument.



4. OPERATION OF PLC

4.1. LADDER DIAGRAM & STATEMENT LIST

000

Network 1

Notice of Soil

When press the button one, I 0.0 input will operated and heater (Q 0.0) is operated as timer count as.

Network 2

Schwork.

When I 0.0 is active, counter (C0) count one and when press the button seven, it will be reset.

Network 3

After the counter (C0) count one, timer (T36) will counted thirty sec.

Network 4

When press the button two (three times), I 0.4 input will active and heater (Q 0.4) would be operated as timer count as.

Network 5

When I 0.4 is active, the counter (C1) count two and it will be reset when press the button seven.

Network 6

After counter (C1) count, timer (T38) count sixty sec.

Network 7

When we press the button eight, I 0.1 input is active and washing machine (Q 0.1) will operate.

Network 8

When the button nine was pressed, I 0.2 input will active and microwave oven $(Q \ 0.2)$ would operated as timer count as.

Network 9

When I 0.2 is active, counter (C2) counts one. And it will reset with button seven.

Network 10

When counter (C2) counts one, timer (T39) will count thirty sec.

Network 11

When the button five was pressed (three times), I 0.3 input would be active and microwave oven (Q 0.5) will operate as timer count as.

Network 12

When I 0.3 is operate, counter (C3) will count two and when pressing the button seven, it will be reset.

Network 13

After counter (C3) counted, the timer would count sixty sec.

Network 14

The operation will finish.

TITLE COMMENTS

ment 1

the belp and example program

Heater operation for 30 sec.

- -



2 Counter count 1



Timer count 30 sec.





Counter count 2.

and 4



Serwork 6 Timer count 60 sec.



Network 7 Washing machine operation





Counter count 1.

and I



10 Timer count 30 sec.













Setwork 14 Operation will finish.



Heater operation for 30 sec. I0.0 20.0 --//Counter count 1 I0.0 I0.7 CO CO T37, +180 CO T37, +180 CORK 4 //Heater operation for 60 sec. I0.4 T38 Q0.4 COUNTER count 2. I0.4 I0.7 CO, +1 ED 10.7 CTU C1, +2 LD C1 //Timer count 60 sec. TON T38, +360 TWORK 7 //Washing machine operation LD I0.1 = Q0.1 NETWORK 8 //Microwave oven operation for 30 sec. LD 10.2 AN т39 Q0.2 = Q NETWORK 9 //Counter count 1. The second second second second LD I0.2 LD 10.7 5 CTU C2, +1 NETWORK 10 //Timer count 30 sec. T39, +180 TON NETWORK 11 //Microwave oven operation for 60 sec. 10.3 52 LD T36 53 AN Q0.2 54 = 55 56 NETWORK 12 //Counter count 2. LD 10.3 LD 10.7 LD 58 СТИ СЗ, +2 59 **51 NETWORK** 13 //Timer count for 60 sec. 62 LD C3 T36, +360 63 TON 65 NETWORK 14 //Operation will finish. 66 MEND

CONCLUSION

The aim of the study is showing that any process can be managed remotely with easy. Need for remote managing could appear in health-critical or dangerous conditions, being far away job, etc. It could be extremely useful for managers to check or administer.

In fact, a production unit may have a PLC or other types of control device on their processes, so that they may not need this part of job. In this case, if some computers make the data collection and control the process with telephone lines.

In our study, since the telephone lines are live, the processes are controlled in seconds easily. Of course if the destination number is in local area, only dialling will be faster therefore the process will be faster.

In practice, after answering the telephone the tele-secretary will be activated and direct the user by its voice commans.

Our study enables user perform processes twice for safety the password may be set. As human life is busy or be far away from their houses and factories. The remote control becomes very important, since most of equipments are controlled by telephone line.

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	1N4001 ·	1N4	100	7				
E 4				1				
Features	and instheme drop		1	2				
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		4001 4	4002	4003 4004	0.00	200	1000	V
V	Peak Repetitive Reverse Voltage	4001 4 50	100	200 400	600	800	1000	V
VRRM	Peak Repetitive Reverse Voltage Average Rectified Forward Current.	4001 4 50	1002	200 400	600	800	1000	V A
V _{rabin} If(av)	Peak Repetitive Reverse Voltage Average Rectified Forward Current 375 * lead length @ T ₄ = 75°C	50	100	200 400	600	800	1000	A
Verrin If(av) If5m	Peak Repetitive Reverse Voltage Average Rectified Forward Current .375 * lead length @ T _A = 75°C Non-repetitive Peak Forward Surge	4001 4 50	100	200 400 1.0 30	600	800	1000	A
Vrbba If(av) IfSM	Peak Repetitive Reverse Voltage Average Rectified Forward Current .375 * lead length @ T _A = 75°C Non-repetitive Peak Forward Surge Current 8.3 ms Single Half-Sine-Wave	50	109	200 400 1.0 30	600	800	1000	A A C
Virina If(av) Ifean	Peak Repetitive Reverse Voltage Average Rectified Forward Current 	4001 4	100	200 400 1.0 30 -55 to +17	600 75 75	800	1000	A A C °C
V 18864 IF (AV) IF 549 T 549	Peak Repetitive Reverse Voltage Average Rectified Forward Current. 375 * lead length @ T _s = 75°C Non-repetitive Peak Forward Surge Current 8.3 ms Single Half-Sine-Wave Storage Temperature Range Operating Junction Temperature	4001 4	1002	200 400 1.0 30 -55 to +11 -55 to +11	600 75 75	800	1000	A A °C °C
V _{RRM} IF(AV) IFSM T_stg T_J	Peak Repetitive Reverse Voltage Average Rectified Forward Current 375 * lead length @ T _A = 75°C Non-repetitive Peak Forward Surge Current 8.3 ms Single Half-Sine-Wave Storage Temperature Range Operating Junction Temperature e linking subsestative which the service addition of any service	4001 4 50 Inductor davic	4002 100	200 400 1.0 30 -55 to +1 -55 to +1	600 75 75	800	1000	A A C °C
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VRHM IF(AV) IF5M T_stg T_J These ratings a Therma Symbol	Peak Repetitive Reverse Voltage Average Rectified Forward Current 	4001 4 50	4002 100	4003 400 200 400 1.0 30 -55 to +17 -55 to +17 mpsired. Value 2.0	600 75 75	008	1000	V A A °C °C Units
V ₁₈₈₄ I _{F(M)} I _{FSM} T _{sb} T _s These raings a Therma Symbol Pp	Peak Repetitive Reverse Voltage Average Ractified Forward Current 375 " lead length @, T _A = 75°C Non-repetitive Peak Forward Surge Current 8.3 ms Single Half-Sine-Wave Storage Temperature Range Operating Junction Temperature re initing values above which the serviceability of any semice I Characteristics Parameter Power Dissipation	4001 4 50 anductor devic	4002 100	4003 400 200 400 1.0 30 -55 to +17 -55 to +17 -5	600 75 75	008	1000	V A A °C °C °C
V _{R884} I _{F(M)} I _{FS61} T ₃ T ₃ These raings a Therma Symbol P _D Ros	Peak Repetitive Reverse Voltage Average Ractified Forward Current. .375 * lead length @ T _A = 75°C Non-repetitive Peak Forward Surge Current .8.3 ms Single Half-Sine-Wave Storage Temperature Range Operating Junction Temperature re initing values above which the serviceability of any service I Characteristics Parameter Power Dissipation Thermal Resistance, Junction to Ambient	4001 4 50 anductor devic	4002 100 se may be i	4003 400 200 400 1.0 30 -55 to +11 -55 to +11 mpsited. Value 3.0 50	600 75 75	008	1000	V A A C C C C Units W C CW
V ₁₈₈₄ I _{F (M)} I _{F SM} T ₃ T ₃ Therma Symbol P _D R _{a,M}	Peak Repetitive Reverse Voltage Average Ractified Forward Current. .375 * lead length @ T _A = 75°C Non-repetitive Peak Forward Surge Current <u>8.3 ms Single Half-Sine-Wave</u> Storage Temperature Range Operating Junction Temperature e linking values above which the serviceability of any service I Characteristics Parameter Power Dissipation Thermal Resistance, Junction to Ambient	4001 4 50 and and actor device	4002 100 se may be i	4003 400 200 400 1.0 30 -55 to +11 -55 to +11 mpaired. Value 3.0 50	600 75 75	008	1000	V A A C C C C Units W C CW
V _{R84} I _{F (44)} I _{F 541} T ₃ Therma Symbol P _D Raw Electric	Peak Repetitive Reverse Voltage Average Ractified Forward Current .375 * lead length @ T _A = 75°C Non-repetitive Peak Forward Surge Current <u>8.3 ms Single Half-Sine-Wave</u> Storage Temperature Range Operating Junction Temperature e limiting values above which the serviceability of any service I Characteristics Parameter Power Dissipation Thermal Resistance, Junction to Ambient	4001 4 50 Inductor deviz	to U2 100 se may be i	4003 400 1.0 1.0 30 -55 to +11 -55 to +11 mpaired. Value 3.0 50	600 75 75	800	1000	V A C C C C Vnits W C/W
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V _{F884} I _{F(M)} I _{FSM} T _{abp} T _a These rainge a Therma Symbol P _D Raw Electric Symbol V _F	Peak Repetitive Reverse Voltage Average Rectified Forward Current. 375 * lead length @ T _A = 75°C Non-repetitive Peak Forward Surge Current 8.3 ms Sindle Half-Sine-Wave Storage Temperature Range Operating Junction Temperature et in ling values above which the serviceability of any semico I Characteristics Parameter Power Dissipation Thermol Resistance, Junction to Ambient cal Characteristics T _A = 25°C unit Parameter	4001 c 50 anductor davic ass otherwise 4001	4002 100 noted 4002	4003 400 1.0 30 -55 to +11 -55 to +11 -55 to +11 mpaired. Value 3.0 50 Devic 4003 400 1.1 200	600 75 75 9 •	800 5 4006	1000 5 4007	V A A C C C C C C V Units W C/W
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Vrssar Ir(M) Ir(M) Ir(M) Ir(M) T_stg T_J Therma Symbol PD Raw Electric Symbol Vr Ir	Peak Repetitive Reverse Voltage Average Rectified Forward Current. 375 * lead length @ T _A = 75*C Non-repetitive Peak Forward Surge Current 8.3 ms Sindle Half-Sine-Wave Storage Temperature Range Operating Junction Temperature re inling values above which the serviceability of any semice I Characteristics Parameter Power Dissipation Thermal Resistance. Junction to Amblem Cal Characteristics Parameter Forward Voltage @ 10 A Maximum Full Load Reverse Current. Fu Cycle T _A = 75*C	4001 4 50 anductor device ess otherwise 4001	noted	4003 400 1.0 1.0 30 -55 to +17 -55 to +17 -55 to +17 -55 to +17 -55 to	600 75 75 2 2 4 4 400	800 5 4006	1009 5 4007	V A A C C C C C V Units V C/W V Units V V μΑ μΑ
V ₁₈₈₄ I _{F(M)} I _{F(M)} I _{F(M)} Taip Therma Symbol Pip Raw Electric Symbol V _F I _a - - - - - - - - - - - - -	Peak Repetitive Reverse Voltage Average Rectified Forward Current. 375 * lead length @ T _A = 75°C Non-repetitive Peak Forward Surge Current 8.3 ms Sindle Half-Sine-Wave Storage Temperature Range Operating Junction Temperature re initing values above which the serviceability of any service I Characteristics Parameter Power Dissipation Thermal Resistance. Junction to Amblem Cal Characteristics Parameter Porward Voltage @ 1.0 A Maximum Full Load Reverse Current, Fu Cycle T _A = 25°C unit Parameter Forward Voltage @ 1.0 A	4001 4 50 anductor device ess otherwise 4001	noted	200 400 1.0 1.0 30 -55 to +17 -55 to +17 -55 to +17 mpaired. Value 3.0 50 Devic 4003 400 1.1 30 50 50 50 50 50 50 50 50 50 5	600 75 75 29 20 4 400	800	1009 5 4007	V A A C C C C C Units V V C/W
V ₁₈₈₄ I _{F(M)} I _{F(M)} I _{F(M)} T _{abp} T _a Therma Symbol P _D R _{GM} Electric Symbol V _F I _x I _x	Peak Repetitive Reverse Voltage Average Ractified Forward Current 375 * lead length @ T _A = 75°C Non-repetitive Peak Forward Surge Current 8.3 ms Sindle Half-Sine-Wave Storage Temperature Range Operating Junction Temperature re initing values above which the serviceability of any semice I Characteristics Parameter Power Dissipation Thermal Resistance, Junction to Amblem Cal Characteristics T _A = 25°C unit Parameter Forward Voltage @ 1.0 A Maximum Full Load Reverse Current, Fu Cycle T _A = 75°C Reverse Current @ rated V _R T _A = 25°C	4001 4 50 snductor device ess otherwise 4001	4002 100 rs may be i noted	4003 400 1.0 30 -55 to +17 -55 to +17 -55 to +17 -55 to +17 mpsited. Value 3.0 50 Devic 4003 400 1.1 30 5.0 5.0 1.5 5.0 5.0 1.5 5.0 1.0 5.0 1.0 5.5 5.0 1.0 5.5 5.0 1.0 5.5 5.0 1.0 5.5 5.0 1.0 5.5 5.0 1.0 5.5 5.0 1.0 5.5 5.0 1.0 5.5 5.0 1.0 5.5 5.0 1.0 5.5 5.0 1.0 5.5 5.0 1.0 5.5 5.0 1.0 5.5 5.0 1.0 5.5 5.0 1.0 5.5 5.0 1.0 5.5 5.0 1.0 5.5 1.0 5.5 1.0 5.5 1.0 5.5 1.0 5.5 1.0 5.5 1.0 5.5 1.0 5.5 1.0 5.5 1.0 5.5 1.0 5.5 1.0 5.5 1.0 5.5 1.0 5.5 1.0 5.5 1.1 5.5 1.0 5.5 1.1 5.0 5.0 5.0 5.0 5.0 5.0 5.0 5.0	600 75 75 9 9 2 9	800 5 4006	1009 5 4007	V А А °C °C °C °C V Units V °C/W °С/W °С/W °С/W °С/W °С/W °С/W

C2003 Faircluid Somiconductor Compension



TRADEMARKS			to the sume or in sutherin	red to use and is
The following are reg not intended to be an ACEx TM ActiveArray TM Bottomless TM CoolFET TM CROSSVOLT TM DOME TM EcoSPARK TM ErSigna TM Across the board The Power France DecorramableA	jstered and unregistered tri exhaustive list of all such FACT Tal FACT Quiet Series™ FAST FAST FAST FAST Tal FRFET™ GlobalOptoisolator™ GTO™ HiSeC™ I ² C™ I. Around the world.™ thise™	ademarks Fairchild Semico trademarks. Implied Disconnect Tu ISOPLANAR Tu LittleFETTu MicroFETTu MicroPak Tu MICROWIRETu MSXTu MSXTu MSXTru OCXTu OCXTu OCXTu OCXProTu OPTOLOGIC [®] OPTOPLANARTu	PACMAN ^{TU} POP ^{TU} Power247 ^{TU} PowerTrench [®] QFET ^{TU} QS ^{TU} QT Optoelectronics ^{TU} Quiet Series ^{TU} RapidConfigure ^{TU} RapidConfigure ^{TU} SILENT SWITCHER [®] SMART START ^{TU}	SPM TM Stealth TM SuperSOT TM -6 SuperSOT TM -6 SuperSOT TM -6 SyncFET TM TinyLogic [®] TruTranslation ^{TI} UHC TM UHtraFET [®] VCX TM

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AIRCHILE

NOL CTORT

CD4013BC **Dual D-Type Flip-Flop**

General Description

The CD4013B dual D-type flip-flop is a monolithic complementary MOS (CMOS) integrated circuit constructed with N- and P-channel enhancement mode transistors. Each fip-flop has independent data, set, reset, and clock inputs and "O" and "O" outputs. These devices can be used for shift register applications, and by connecting "Q" output to the data input, for counter and toggle applications. The logic level present at the "D" input is transferred to the Q output during the positive-going transition of the clock pulse. Setting or resetting is independent of the clock and is accomplished by a high level on the set or reset line respectively.

Features

- Wide supply voltage range: 3.0V to 15V
- High noise immunity: 0.45 Vpp (typ.)
- Low powerTTL: fan out of 2 driving 74L compatibility: or 1 driving 74LS

Applications

- · Automotive
- Data terminals
- Instrumentation
- Medical electronics
- Alarm system
- Industrial electronics
- Remote metering
- · Computers

Ordering Code:

M14A	14 Lead Small Outline integrated circuit (Contract
CD4013BCIVI	PLATTYPE II, 5.3mm Wide
CD4013BCSJ M14D	14-Lead Small Outline Package (SCF), EDR JEDEC MS-001, 0.300" Wide
CD4013BCN N14A	14-Lead Plastic Dual-In-Line Package (1 Dw), out and





0 0 0 0 1 1 0 0 1 0 X 0 0 0 1 0 X 0 0 0 1 0 X 0 1 1 0 1 x X 0 1 1 0 1 1 Change Don't Care Case te 1: Level Change Example Example	D O O O I - 1 0 0 1 0 - X 0 D Q Q x X 1 0 0 1 x X 0 1 1 0 x X 0 1 1 0 x X 1 1 1 1 Change Don't Care Case e 1: Level Change E	CL (Note 1)	D	R	S	Q	Q
	- 1 0 0 1 0 - X 0 0 Q Q x X 1 0 0 1 x X 0 1 1 0 x x 1 1 1 1 Change Don't Care Case e 1: Level Change	-	0	0	0	0	1
x 0 0 Q Q x x 1 0 0 1 x x 0 1 1 0 x x 1 1 1 1 Change Don't Care Case e 1: Level Change	x 0 0 Q Q x x 1 0 0 1 x x 0 1 1 0 x x 1 1 1 1 x x 1 1 1 1 Change Don'Care Case e 1: Level Change Envel Change Envel Change Envel Change	_	1	0	0	1	0
x x 1 0 0 1 x x 0 1 1 0 x x 0 1 1 0 x x 1 1 1 1 Change Don't Care Case Is 1: Level Change Level Change Level Change Level Change	x x 1 0 0 1 x x 0 1 1 0 x x 1 1 1 1 Change Don't Care Case e 1: Level Change e 1 1 1	-	x	0	D	Q	Q
x x 0 1 1 0 x x 1 1 1 1 Change Don't Care Case a 1: Level Change 1 1 1	x x 0 1 1 0 x x 1 1 1 1 Change Don't Care e 1: Level Change	x	x	1	0	0	1
X X 1 1 1 1 Change Don't Care Case le 1: Level Change	X X 1 1 1 1 Change Don't Care Case e 1: Lewel Change	x	x	ō	1	1	0
Change Don't Care Case Le 1: Level Change	Change Don't Care Case e 1: Lewel Change	x	×	1	1	1	1
		X Change Don't Care C	X ase nange	1	1	1	1
		e 1: Level C					

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Absolute Maximum Ratings(Note 2)

(Note 3)

DC Supply Voltage (V _{DD}) Input Voltage (V _{IN}) Storage Temperature Range (T _S)	-0.5 V _{DC} to +18 V _{DC} -0.5 V _{DC} to V _{DD} +0.5 V _{DC} -65°C to +150°C
Power Dissipation (PD)	700
Duat-In-Line	700 m%
Small Outline	500 m₩
Lead Temperature (T _L) (Soldering, 10 seconds)	260°C

Recommended Operating Conditions (Note 3)

DC Supply Voltage (VDD)

Input Voltage (VIN)

0 Vpc to Vpp Vpc

-55°C to +125°C

+3 Vpc to +15 Vpc

CD4013BC

Operating Temperature Range (T_A)

Note 2: "Absolute Maximum Ratings" are those values beyond which the salety of the device cannot be guaranteed, they are not meant to imply that the devices should be operated at these limits. The tables of "Recom-mended Operating Conditions" and "Electrical Characteristics" provide con-ditions for actual device operation.

Note 3: $V_{\rm SS}$ = 0V unless otherwise specified.

DC Electrical Characteristics (Note 3)

			-55°C		+25°C			+120	Units	
Symbol	Parameter	Conditions	Min	Мах	Min	Тур	Мак	Min	Məx	
00	Quiescent Device Current	$\begin{split} V_{DD} &= 5V, \ V_{IN} = V_{DD} \ \text{or} \ V_{SS} \\ V_{DD} &= 10V, \ V_{IN} = V_{DD} \ \text{or} \ V_{SS} \\ V_{DD} &= 15V, \ V_{IN} = V_{DD} \ \text{or} \ V_{SS} \end{split}$		1.0 2.0 4.0			1.0 2.0 4.0		30 60 120	μА
Vol	LOW Level Output Voltage	_D < 1.0 μA V _{DD} = 5V V _{DD} = 10V V _{DD} = 15V		0.05 0.05 0.05			0.05 0.05 0.05		0.05 0.05 0.05	V
VOH	HIGH Level Output Voltage	_D < 1.0 μA V _{DD} = 5V V _{DD} = 10V V _{DD} = 15V	4.95 9.95 14.95		4.95 9.95 14.95			4.95 9.95 14.95		v
VIL	LOW Lavel Input Vollage	$\begin{split} \ \mathbf{b} \ _{0} &< 1.0 \ \mu A \\ V_{DD} &= 5V, \ V_{D} &= 0.5V \ \text{or} \ 4.5V \\ V_{DD} &= 10V. \ V_{O} &= 1.0V \ \text{or} \ 9.0V \\ V_{DD} &= 15V, \ V_{O} &= 1.5V \ \text{or} \ 13.5V \end{split}$		1.5 3.0 4.0			1.5 3.0 4.0		1.5 3.0 4.0	v
VIH	HIGH Level Input Voltage	$\begin{split} & I_O < 1.0 \ \mu\text{A} \\ & V_{DD} = 5\text{V}, \ V_O = 0.5\text{V} \ \text{or} \ 4.5\text{V} \\ & V_{DD} = 10\text{V}, \ V_O = 1.0\text{V} \ \text{or} \ 9.0\text{V} \\ & V_{mn} = 15\text{V}, \ V_O = 1.5\text{V} \ \text{or} \ 13.5\text{V} \end{split}$	3.5 7.0 11.0		3.5 7.0 11.0			3.5 7.0 11.0		v
loi.	LOW Level Output Current (Note 4)	$V_{DD} = 5V, V_D = 0.4V$ $V_{DD} = 10V, V_O = 0.5V$ $V_{DD} = 15V, V_D = 1.5V$	0.64 1.6 4.2		0.51 1.3 3.4	0.88 2.25 8.8		0.36 0.9 2.4		mA
юн	HIGH Level Output Current (Note 4)	$V_{DD} = 15V, V_{O} = 4.6V$ $V_{DD} = 5V, V_{O} = 4.6V$ $V_{DD} = 10V, V_{O} = 9.5V$ $V_{DD} = 15V, V_{O} = 13.5V$	-0.64 -1.6 -4.2		-0.51 -1.3 -3.4	-0.88 -2.25 -8.8		-0.36 -0.9 -2.4		mA
ĨIN	Input Current	$V_{DD} = 15V, V_N = 0V$ $V_{DD} = 15V, V_N = 15V$		-0.1 0.1		-10 ⁻⁵ 10 ⁻⁵	-0.1 0.1		-1.0	μA

Note 4: $I_{\Box H}$ and $I_{\Box L}$ are measured one output at a time.

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$T_{\Delta} = 25^{\circ}C, C_{L}$	= 50 pF, R_L = 200k, unless otherwise no	ted Conditions	Min	Тур	Мах	Units
Symbol	Parameter		1			
LOCK OPERAT	TION	Man = 5V	1	200	350	
PH. WLH	Propagation Delay Time	Ven - 10V	1 1	80	160	ns
		$V_{\rm em} = 15V$		65	120	_
		Vio = 5V	1	100	200	
true true	Transition Time	V 108/		50	100	ns
		$v_{DD} = 15V$		40	80	
		Vice - SV		100	200	
has . had-	Minimum Clock	$V_{\rm DD} = 400$		40	80	กร
	Pulse Width	$V_{\rm DD} = 15V$		32	65	
		V_00 = 5V			15	
IRCL. UPCL	Maximum Clock Rise and	Ven = 10V			10	μs
	Fall Time	VDD = 15V			.5	
		V00 = 15V		20	40	
teau	Minimum Set-Up Time	$V_{\rm DD} = 10V$		15	30	กร
		$V_{DD} = 15V$		12	25	
		Vers = 5V	2.5	5		
fci	Maximum Clock	Ven = 10V	6.2	12.5		IVR-1
C.	Frequency	$V_{DD} = 15V$	7.8	15.5		
		1.07			000	
SET AND RE	SET OPERATION	Vras = 5V		150	300	
tpHL(R)	Propagation Delay Time	$V_{DD} = 10V$		65	130	113
tpLH(S)		Vnn = 15V		45	90	
		Vno = 5V		90	180	
twitt(R)-	Minimum Set and	Vnn = 10V		40	80	112
twies)	Reset Pulse Width	Wrone 15V		25	50	
		*10 = 10.		5	7.5	p p

CIN Average Input Capacitance Note 5: AC Parameters are guaranteed by DC correlated testing.

Switching Time Waveforms



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SUTLINE OPTOCOUPLERS

Size does matter, but bigger isn't always better.

Portable and compact devices require optocouplers that deliver the performance of a standard 4- or 8-pin dual inline package (DIP), but occupy only a fraction of the space.

Fairchild Semiconductor's small outline package (SOP) optocouplers meet that need.

AN SO-8 PACKAGE HAS A 69% SMALLER FOOTPRINT THAN AN 8-PIN DIP



SO-8 Package

A FULL-PITCH MINI-FLAT PACKAGE HAS A 37% SMALLER FOOTPRINT THAN A 4-PIN DIP



Full-Pitch Mini-Flat Package



Half-Pitch Mini-Flat Package A HALF-PITCH MINI-FLAT PACKAGE HAS A 61% SMALLER FOOTPRINT THAN A 4-PIN DIP



For more information, including data sheets, go to www.fairchildsemi.com/sopopto

SO-8 Package Optocouplers

High-Speed (1 Mbit/s) Transistor Output, GaAsP Input Optocoupler High-Speed (10 Mbit/s) Logic Gate Output, GaAsP Input Optocoupler High-Gain (>300% CTR) Split Darlington Output, GaAsP Input Optocoupler Phototransistor Output, GaAs Input Optocoupler Photodarlington Output, GaAs Input Optocoupler Transistor Output, AC GaAs Input Optocoupler Dual-Channel Phototransistor Output, GaAs Input Optocoupler Dual-Channel Photodarlington Output, GaAs Input Optocoupler

Full- and Half-Pitch Mini-Flat Package Optocouplers

Phototransistor Output, GaAs Input Optocoupler Phototransistor Output, AC GaAs Input Optocoupler

Safety Regulatory Agency Approvals BSI, CSA and UL certified.

Tape and Reel Ordering Information

Option R1 – 500 devices per reel, 7 inch (178 mm) reel diameter Option R2 – 2,500 devices per reel, 13 inch (330 mm) reel diameter

Footprint Drawings for PCB Layout



For more information, including data sheets, go to www.fairchildsemi.com/sopopto

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SO-8 Package High Speed Transistor Output **Optocouplers**

4	Г	-	
R	A	- 2	
3		6	
1		4	

CTI 16 mA min	₹# 1 _f (%) max	V _{CIL} (V) EBIAK	lca. (µA) max	T _{ME} /T _{R.H} (µs) max	V _{IND} AC [RIMS]
	6.0	0.4	200	0.8/0.8	2.5 KV
19	50	0.4	200	1.5/1.5	2.5 kV
1	50	0.4	200	0.8/0.8	2.5 kV
	CTT 16 mA min 19 7	CTR # 16 mA l _f (%) min max 19 50 7 50 10 50	CTR Vol 16 mA I _f (%) (V) min max 19 50 7 50 0.4 50 0.4	CTR VCL Ical. 16 mA Ir (%) (M) (µA) min max max 19 50 0.4 200 7 50 0.4 200 10 50 0.4 200	СТК = V ск. Iсс. Тня/Текл. 16 mà Ir 9%) (V) (µA) (µB) min max max max 19 50 0.4 200 0.8/0.8 7 50 0.4 200 1.5/1.5 10 50 0.4 200 0.8/0.8

*Base not connected for HCPL-0152

SO-8 Package High Speed Logic Gate Optocouplers



Port Number	l _{in} (mA) max	V _{OL} (V) max	CMH/CML (KV/µs) min	loci (mA) max	Tern/Tern (ms) max	V _{BO} AC [RMS]
		06		13.	75/75	2.5 KV
HCP1-0600	5	0.6	5	13	75/75	2.5 KV
HCPL-0601	5	0,0				

Vot (V) max

0.4

0.4

CTR #

1.6 mA 4 (94)

2600

2600 500

min max

300

Part Number

HCPL-0700

HCPL-0701

HOH (HA)

max

250

100

SO-8 Package High Gain Split Darlington Optocouplers

Full-Pitch Mini-Flat Package 4-Pin Optocouplers



Part Number	CTF 5 mA min	(%) max	BV _{CEO} (V) min	BV _{ECO} (V) Millio	t _R /t _l (µs) typical	Vino AC [RIVIS]
		600	30	7	3/3	3.75 kV
HMA121	30	1000	90	7	3/3	3.75 KV
HMA124	100	1200	00		2/2	3,75 kV
HMA2701	50	300	40			2 TE MI
HM662705	50"	3001	40	7	3/3	3.10 MV

°CTR measured at I₁ = ±5 mA

T_{HR}/T_{ELH} (µs) max

10/35

25/60

VISO AC [RMS]

2.5 kV

2.5 KV

HMA121, HMA124, HMA2701

Half-Pitch Mini-Flat Package 4-Pin Optocouplers

1-0	
HMHAA280	L.

F
HMHA281, HMHA2801

Part Number	CTF 5 mA min	t (%) max	BV _{CEO} (V) min	BV _{ICO} (V) min	yeAr (µs) typical	Visio AC [RIMS]
	-	c00	90	7	3/3	2.5 kV
HMHA281	50	600-	80	7	3/3	2.5 KV
HMHAA280	50"	600		7	3/3	2.5 kV
HMHA2801	80	600	- 61	-	+CTP model	red at h - ±5 m

For more information, including data sheets, go to www.fairchildsemi.com/sopopto

SO-8 Package Phototransistor Output GaAs Input Optocouplers



10 mA min	i∉ (%) max	BV cro- (V) min	(V) min	(µs) typical	Vpo AC (RMS)
1.40	80	70	7	3.0/2.8	3.0 KV
40	195	70	7	3.0/2.8	3.0 KV
63	125	70	7	3.0/2.8	3.0 KV
100	euro -	70	7	3.0/7.8	3.0 KV
40	125	10	7	7 5/5.7	3.0 KV
20		30		75/57	3.0 KV
50		30	1	7 5/57	3.0 KV
100		30	1	1.0/0.1	2011
20"		30	7	7.5/5.7	3.0 64
50"		30	7	7.5/5.7	3.0 KV
100*		30	7	7,5/5.7	3.0 KV
	10 mA min 40 63 190 40 20 50 100 20° 50° 50° 100°	10 mA \$ (%) min max 40 80 63 125 100 200 40 125 100 200 40 125 100 50 100 200 500 200* 50* 50* 100*	10 mA ↓ (%) min (V) min 40 80 70 63 125 70 40 209 70 40 125 70 40 125 70 20 30 50 30 50 30 20° 30 50° 30 20° 30 100 30 20° 30	Ibmak (%) (V) (V) min max min min 40 80 70 7 63 125 70 7 100 200 70 7 40 125 70 7 20 30 7 50 300 7 100 30 7 20 30 7 50 30 7 50 30 7 50 30 7 50 30 7 50 30 7 50* 30 7 50* 30 7 50* 30 7 50* 30 7	IomA (%) (V) (V) (µs) min max min min typical 40 80 70 7 3.0/2.6 63 125 70 7 3.0/2.8 100 200 70 7 3.0/2.8 40 125 70 7 3.0/2.8 40 125 70 7 3.0/2.8 20 30 7 7.5/5.7 50 30 7 7.5/5.7 100 30 7 7.5/5.7 20° 30 7 7.5/5.7 100 30 7 7.5/5.7 20° 30 7 7.5/5.7 50° 30 7 7.5/5.7 50° 30 7 7.5/5.7 50° 30 7 7.5/5.7 100° 30

SO-8 Package Photodarlington Output GaAs Input Optocoupler



Part Number	CTF 1 mA min	t (%) 4 (%) max	BV _{CEO} (V) min	BV _{ERD} (V) min	ton/torr (µs) typical	VBO AC [RMIS]
	500		30	7	3.5/95.0	3.0 KV

SO-8 Package Transistor Output AC Input Optocoupler



Part Number	CTI ±10 m min	₹#₽ A ↓ (%) max	BV _{CEO} (V) min	BV _{EDO} (V) min	ton/ton (µs) typical	VBO AC [RMS]
			30	5	-	3.0 kV

SO-8 Package Dual Channel Phototransistor Output GaAs Input Optocouplers

SO-8 Package Dual Channel Photodarlington Output GaAs Input Optocoupler



Part	CTF 10 mA min	t (%c) max	BV _{CED} (V) min	BV _{ERO} (V) min	tow ^{(t} orr (µs) typical	V _{BO} AC (RMIS)
NUMBER	100	100	70	7	3.0/2.8	3.0 KV
MOCD207	100	200			3028	3.0 KV
MOCD208	40	125	70	1	Jankin	2014
D211	20		30	7	7.5/5.7	3.UKV
MOCDZTT	-	-	10	7	3.02.8	3.0 KV
MOLD213	100				7 5/5 7	3.0 KV
MOCD217	100"		30	7	1.575.7	

Part	CTR # 1 mA \ (%) min max		BV _{CEO} (V) nvin	(V) min	(µs) (ypicat	VISO AC (RMS)
		-	20	7	35/95.0	3.0 kV

For more information, including data sheets, go to www.fairchildsemi.com/sopopto

M74HC192

SYNCHRONOUS UP/DOWN DECADE COUNTER

- HIGH SPEED : $f_{MAX} = 55 \text{ MHz} (TYP.) \text{ at } V_{CC} = 6V$
- LOW POWER DISSIPATION:
 I_{CC} =4μA(MAX.) at T_A=25°C
- HIGH NOISE IMMUNITY: $V_{NIH} = V_{NIL} = 28 \% V_{CC}$ (MIN.)
- SYMMETRICAL OUTPUT IMPEDANCE: |I_{OH}| = I_{OL} = 4mA (MIN)
- BALANCED PROPAGATION DELAYS:
- WIDE OPERATING VOLTAGE RANGE:
 V_{CC} (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 192

DESCRIPTION

The M74HC192 is an high speed CMOS SYNCRONOUS UP/DOWN DECADE COUNTERS fabricated with silicon gate C²MOS echnology.

The counter has two separate clock inputs, an UP COUNT input and a DOWN COUNT input. All supputs of the flip-flop are simultaneously gegered on the low to high transition of either ock while the other input is held high. The rection of counting is determined by which input clocked. This counter may be preset by entering the desired data on the DATA A, DATA B, DATA and DATA D input. When the LOAD input is the low the data is loaded independently of the clock input. This feature allows the counters be used as divide-by-n counters by modifying the count length with the preset inputs. In addition

PIN CONNECTION AND IEC LOGIC SYMBOLS



ORDER CODES

PACKAGE	TUBE	T&R
DIP	M74HC192B1R	
SOP	M74HC192M1R	M74HC192RM13TR
TSSOP		M74HC192TTR

the counter can also be cleared. This is accomplished by inputting a high on the CLEAR input. All 4 internal stages are set to low independently of either COUNT input. Both a BORROW and CARRY output are provided to enable cascading of both up and down counting functions. The BORROW output produces a negative going pulse when the counter underflows and the CARRY outputs a pulse when the counters overflows. The counter can be cascaded by connection the CARRY and BORROW outputs of one device to the COUNT UP and COUNT DOWN inputs, respectively, of the next device. All inputs are equipped with protection circuits against static discharge and transient excess voltage.



ETRHC192

AND OUTPUT EQUIVALENT CIRCUIT



- V _{CC} V _{CC} -	
GND GND	SC03650

PIN No	SYMBOL	NAME AND FUNCTION
3, 2, 6, 7	QA to QD	Flip-Flop Outputs
4	COUNT DOWN	Count Down Clock Input
5	COUNT UP	Count Up Clock Input
11	LOAD	Asynchronous Parallel Load Input (Active LOW)
12	CARRY	Count Up (Carry) Output (Active LOW)
13	BORROW	Count Down (Borrow) Output (Active LOW)
14	CLEAR	Asynchronous Reset Input (Active High)
15, 1, 10, 9	A to D	Data Inputs
8	GND	Ground (0V)
16	Vcc	Positive Supply Voltage

TRUTH TABLE

COUNT DOWN	LOAD	CLEAR	FUNCTION
н	Н	L	COUNT UP
н	н	L	NO COUNT
	н	L	COUNT DOWN
			NO COUNT
			PRESET
X	L	н –	RESET
	COUNT DOWN H H 	COUNT DOWNLOADHHHHHHHXLXX	COUNT DOWNLOADCLEARHHLHHLHLHLXLLXLH

E Don't Care

DEC DIAGRAM



This logic diagram has not be used to estimate propagation delays

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3/14
			~
_		-	
_			
	_		





#BSOLUTE MAXIMUM RATINGS

Trenh al	Parameter	Value	Unit
Symbol		-0.5 to +7	V
Vcc	Supply Voltage	-0.5 to Vcc + 0.5	V
VI	DC Input Voltage		V
Vo	DC Output Voltage	-0.5 to VCC + 0.6	mA
lik	DC Input Diode Current	± 20	
low	DC Output Diode Current	± 20	mA
-OK	DC Output Current	± 25	mA
10	DO V or Cround Current	± 50	mA
CC OF IGND	DC V _{CC} of Glouid Carent	500(*)	mW
PD	Power Dissipation	-65 to +150	°C
T _{stg}	Storage Temperature	-00101100	°C
Ti	Lead Temperature (10 sec)	300	

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is timplied 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Cumbal	Parameter		Value	Unit
Symbol	Querele Mallaga		2 to 6	V
V _{CC}			0 to V _{CC}	V
Vi			0 to V _{CC}	V
Vo	Output Voltage		-55 to 125	°C
Тор		$V_{cc} = 2.0 V$	0 to 1000	ns
	Input Rise and Fail Time	$V_{CC} = 4.5V$	0 to 500	ns
t _r , t _f		$V_{CC} = 6.0V$	0 to 400	ns

ESECIFICATIONS

		Tos	t Condition				Value				
				T _A = 25°C			-40 to 85°C		-55 to 125°C		Unit
lodmed	Parameter	Vcc	-	Min	TVD.	Max.	Min.	Max.	Min.	Max.	
		(•)		4.5			1.5		1.5		
Vie	High Level Input	2.0		1.0			3.15		3.15		V
- 44	Voltage	4.5		3.15			4.2		4.2		
		6.0		4.2		0.5		0.5		0.5	
V.	Low Level Input	2.0			-	1.35		1.35		1.35	V
100	Voltage	4.5			-	1.00		1.8		1.8	
	201	6.0		10	20	1.0	19		1.9		
Vau	High Level Output	2.0	I _O =-20 μA	1.9	2.0		1 1 1		4.4		
-Un	Voltage	4.5	I _O =-20 μΑ	4.4	4.5	-	4.4	-	59		V
		6.0	I ₀ =-20 μA	5.9	6.0	-	5.9	-	1 10	-	1
		45	1 ₀ =-4.0 mA	4.18	4.31		4.13	-	4.10	-	1
	in the second se	6.0	I ₀ =-5.2 mA	5.68	5.8		5.63	0.1	5.00	01	-
24	Low Lovel Output	2.0	I _O =20 μA		0.0	0.1		0.1	-	0.1	1
VOL	Voltage	4.5	l ₀ =20 μA	-	0.0	0.1		0.1	-	0.1	$+$ \vee
		6.0	lo=20 μA		0.0	0.1		0.1	-	0.1	$+$ \cdot
		0.0	lo=4.0 mA		0.17	0.26		0.33		0.40	-
		4.5	15.2 mA		0.18	3 0.26	5	0.33		0.40	-
	1	6.0	10-3.2 11/1			1.0		+ 1		± 1	μ
II.	Input Leakage Current	6.0	$V_{I} = V_{CC}$ or GND		-	± 0.		10	-	80	
lcc	Quiescent Supply	6.0	$V_{I} = V_{CC}$ or GND			4		40		00	1 pt

C192

ECTRICAL CHARACTERISTICS (CL = 50 pF, Input tr = tf = 6ns)

	-	Test	Condition					Value				
		1630		Т	A = 25	°C		-40 to	85°C -55 to		125°C	Unit
100	Parameter	V _{CC} (V)		Min.	Тур.	M	ax.	Min.	Max.	Min.	Max.	
				-	30	-	75		95		110	
THE C	Output Transition	2.0			8		15		19		22	ns
	Time	4.5			7	+	13		16		19	
		6.0			65	-	190		240		285	
- PHL	Propagation Delay	2.0			20	+	38		48		57	ns
	Time (COUNT UP,	4.5			16	+	32		41		48	
	DOVVIN - Cr)	6.0			40	-	130		165		195	
PHL	Propagation Delay	2.0			13		26		33		39	ns
	Time (COUNT UP -	4.5			11		22		28		33	
	CARRT)	6.0			40		130		165		195	
PHL	Propagation Delay	2.0			13		26		33		39	ns
	Time	4.5					22		28		33	
	BORROW)	6.0				_	22		275		330	
	Propagation Delay	2.0			85	5	220		210		66	66 ns
PHL	Time (LOAD - Q)	4.5			2	5	44		30		56	56
		6.0			20	0	37		41		375	
	Propagation Delay	2.0			11	0	250		313		75	ns
- PHL	Time (LOAD -	4.5			3	0	50		63		64	
	CARRY)	6.0			2	5	43		54		27	
	Dropagation Delay	2.0			1'	10	250		31	>	75	
LH YPHL	Time (LOAD -	4.5			3	1	50		63		6/	
	BORROW)	6.0			2	5	43		- 54		20	5
-	Dropagation Delay	2.0			8	30	190		24	0	20	
PLH PHL	Time (DATA - Q)	4.5			2	25	38		48	3		
		6.0			2	20	32		4		27	5
	Propagation Delay	2.0			1	20	250)	31	5	7	5 0
PLH	Time (DATA -	4.5			1	34	50		6	3	6	
	CARRY)	6.0			:	28	43		5	4	27	5
	Bronagation Delay	2.0			1	110	25	0	31	15	7	5 1
PLH PHI	Time (DATA -	4.5				30	50)	6	3		
	BORROW)	6.0				25	43	3	5	4	2	10
	Dranagation Delay	2.0				100	22	5	2	30		
^L PHL	Time (CLEAR -Q)	4.5	1			30	4	5		0		8
		6.0	-			25	3	8	4	8		75
	Propagation Delay	v 2.0				120	25	0	3	15		15
^L PLH	Time (CLEAR	4.5	1			35	5	0		53		34
	-CARRY)	6.0	-			29	4	3		04		375
	Propagation Dela	v 2.0				120	2	50	3	15		75
^I PHL	Time (CLEAR -	4.5	1			35	5	0		03		64
	BORROW)	6.0	-			29	4	3	_	54		
	Maximum Clock	20			5	12			4		5.4	
TMAX	Frequency	4.5	-	-	25	48			20		1/	M
	1 ioquonoj	6.0		-	30	55			24		20	

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-		Tect Con	dition				Value	-			
		Test Con		T _A = 25°C				85°C	-55 to 125°C		Unit
80	Parameter	Vcc	M	lin	Tvp.	Max.	Min.	Max.	Min.	Max.	
		(•)			24	100	-	125	1	150	
	Minimum Pulse	2.0	-	_	34	20	-	25		30	ns
	Width (COUNT UP/	4.5			9	17		21		26	
8	DOWN)	6.0		_	1	75	-	95		110	
-	Minimum Pulse	2.0			34	15	-	19		22] ns
8	Width (LOAD)	4.5	-	_	9	10	-	16	1	19	1
		6.0			1	100	-	125	1	150	
-	Minimum Pulse Width (CLEAR)	2.0			40	100	-	25	-	30	ns
Ħ. (4.5	-		12	20	-	21		26	
		6.0		_	10	75	-	95	1	110	
-	Minimum Set-up	2.0			30	15	-	19	-	22	1 n
2	Time(DATA -LOAD)	4.5	1		9	15	-	16	-	19	1
		6.0			1	13	-	0	-	0	1
-	Minimum Hold	2.0		_	-	0	-	0	-	0	1 r
*	Time	4.5			-	0		0		0	1
		6.0		-	-	0	-	65		75	1
-	Minimum Removal	2.0		1	6	50	-	13	-	15	1
MB	Time (LOAD)	4.5		-	2	10	-	13	-	13	-
		6.0			2	9	-			75	-
	Minimum Removal	Demoval 20			14	50	-	00		15	i r
MER	Time (CLEAR)	4.5			4	10		10		13	-
		60			3	9		1			_

CAPACITIVE CHARACTERISTICS

		Test Condition		Value							
Symbol Parameter				T _A = 25°C			-40 to 85°C		-55 to 125°C		Unit
	Parameter	Parameter V _{CC}		Min.	Тур.	Max.	Min.	Max.	Min.	Max. 10	
		(-7			5			10			pF
CINI	Input Capacitance	5.0			5	10					
C _{PD}	Power Dissipation Capacitance (note	5.0			68						pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + C_{CC}$

C192



 \sim StorF or equivalent (includes jig and probe capacitance) \sim Lour of pulse generator (typically 50Ω)





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WAVEFORM 3 : SETUP AND HOLD TIME (A, B, C, D to LOAD) (f=1MHz; 50% duty cycle)

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FORM 4: MINIMUM REMOVAL TIME (COUNT UP OR DOWN TO CLEAR)

50% duty cycle)



MAVEFORM 5 : MINIMUM REMOVAL TIME (COUNT UP OR DOWN TO LOAD)

=1MHz; 50% duty cycle)



					inch	
-		mm.		nathi	TYP.	MAX.
	MIN.	ТҮР	MAX.	WIIN.		
-	0.51		f	0.020		
1	0.01		1.65	0.030		0.065
8	0.77				0.020	
6		0.5			0.010	
61		0.25	5			0.787
-		1.0	20			
0		85			0.335	
Ξ		0.0			0.100	
e	-	2.54		-	0.700	
e3		17.78				0.280
			7.1	1		0.004
F		-	5.1			0.201
1			-		0.130	
L		3.3		-		0.05





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P001C

CH+C192

					inch	
		mm.			TYP	MAX.
MM.	MIN.	TYP	MAX.	MIN.	ITF.	0.068
			1.75			0.000
^	0.1		0.2	0.003		0.007
al	0.1		1.65			0.064
a2			0.46	0.013		0.018
b	0.35		0.25	0.007		0.010
b1	0.19		0.25		0.019	
C		0.5	459	(4.00)		
c1			45	(typ.)		0.393
D	9.8		10	0.385		0.244
F	5.8		6.2	0.228	0.050	
		1.27			0.050	
9		8.89			0.350	
e3			4.0	0.149		0.157
F	3.8		5.3	0.181		0.208
G	4.6		1.27	0.019		0.050
L	0.5		1.27			0.024
M			0.62			-







PO13H



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		13301 101						
		mm.		inch				
294.	MIN	ТҮР	MAX.	MIN.	TYP.	MAX.		
	inite.		1.2			0.047		
*	0.05		0.15	0.002	0.004	0.006		
#1	0.05	1	1.05	0.031	0.039	0.041		
42	0.8	1	0.30	0.007		0.012		
6	0.19		0.20	0.004		0.0089		
c	0.09		5.1	0.193	0.197	0.201		
D	4.9	5	0.1	0.244	0.252	0.260		
E	6.2	6.4	0.0	0.160	0 173	0.176		
E1	4.3	4.4	4.48	0.109	0.0256 BSC			
е		0.65 BSC			0.0200 000	8°		
к	0°		8°	0°		0.030		
1	0.45	0.60	0.75	0.018	0.024	0.030		









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SEMICONDUCTOR TM

CD4049UBC • CD4050BC Hex Inverting Buffer • Hex Non-Inverting Buffer

General Description

The CD4049UBC and CD4050BC hex buffers are monotinic complementary MOS (CMOS) integrated circuits constructed with N- and P-channel enhancement mode transistors. These devices feature logic level conversion sing only one supply voltage (V_{DD}). The input signal high level (V_{IH}) can exceed the V_{DD} supply voltage when these devices are used for logic level conversions. These devices are intended for use as hex buffers, CMOS to DTL/ TTL converters, or as CMOS current drivers, and at V_{DD} = 5.0V, they can drive directly two DTL/TTL loads over the full operating temperature range.

Features

- Wide supply voltage range: 3.0V to 15V
- Direct drive to 2 TTL loads at 5.0V over full temperature range

October 1987

Revised April 2002

- High source and sink current capability
- Special input protection permits input voltages greater than V_{DD}

Applications

- CMOS hex inverter/buffer
- CMOS to DTL/TTL hex converter
- · CMOS current "sink" or "source" driver
- · CMOS HIGH-to-LOW togic level converter

Ordering Code:

Order Number	Package Number	Package Description
CD4049UBCM	M16A	16-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-012, 0.150* Narrow
CD4049UBCN	N16E	16-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide
CD4050BCM	M16A	16-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-012, 0.150* Narrow
CD4050BCN	N16E	16-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300* Wide
CENTRAL	Town and David Crossile	the approximation the suffix latter "X" to the ordering code.

Connection Diagrams

Pin Assignments for DIP





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Absolute Maximum Ratings(Note 1)

Nate 2)

Supply Voltage (VDD)	-0.5V to +18V
input Voltage (V _{IN}) soltage at Any Output Pin (V _{OUT}) Storage Temperature Range (T _S)	-0.5V to V _{DD} + 0.5V -65°C to +150°C
Power Dissipation (Pp) Dual-In-Line Small Outline	700 mW 500 mW
Lead Temperature (T _L) (Soldering, 10 seconds)	260-0

Recommended Operating Conditions (Note 2)

Cumply Voltage (Ven)	3V to 15V
Suppry voltage (*DD/	0V to 15V
Voltage at Any Output Pin (Vour)	0 to Vod
Operating Temperature Range (TA)	
CD4049UBC, CD4050BC	-55°C to +125°C
Note 1: "Absolute Maximum Ratings" are those	values beyond which the
salety of the device cannot be guaranteed; may a the devices should be operated at these limits mended Operating Conditions" and "Electrical	The table of "Recom- Characteristics" provides

conditions for actual device operation. Note 2: $V_{SS} = 0$ ¥ unless otherwise specified.

DC Electrical Characteristics (Note 3)

		1	-55°C			25°C		+120 0		Units
mbol	Parameter	Conditions	Min	Ыах	Min	Тур	Max	Min	Nax 20	
_	The International Contract	$V_{DD} = 5V$		1.0		0.01	1.0		30	
)	Quiescent Device Content	$V_{en} = 10V$		2.0		0.01	2.0		100	pre
		$V_{pp} = 15V$		4.0		0.03	4.0		120	
	Contract Output Votage	$V_{III} = V_{DD}, V_{III} = 0V,$								
1	COAR FEASI Cother sounds	IIIII < 1 uA							0.05	
	-	$V_{nn} = 5V$		0.05		0	0.05		0.05	
	1	$V_{\rm DD} = 10V$		0.05		0	0.05		0.05	Ŷ
		$V_{DD} = 15V$		0.05		0	0.05		0.05	-
	LOuters Values	$V_{HI} = V_{DPL} V_{HI} = 0V.$								-
OH	HIGH Level Output vokage	III al < 1 IIA						1		
	-	Man an FM	4.95		4.95	5		4.95	1	
	1	$V_{DD} = 40V$	9.95		9.95	10		9,95		V
		$V_{DD} = 15V$	14.95		14.95	15		14,95		-
		VDD - 104								
/IL	LOW Level Input Voltage	101 × 1 µs		1.5		2.25	1.5	1	1.5	
	(CD4050BC Only)	$v_{DD} = 5v, v_{O} = 0.00$		3.0		4.5	3.0		3.0	V V
		$v_{DD} = 10^{\circ}, v_{D} = 1^{\circ}$		4.0		6.75	4.0		4.0	
		V _{DD} = 15V, v ₀ = 1.5V		+	-					
VIL	LOW Level Input Voltage	$ I_0 < I_{\rm per}$		1.0		1.5	1.0		1.0	
	(CD4049UBC Only)	$v_{DD} = 3v, v_D = 4.5v$		2.0		2.5	2.0		2.0	V
		$v_{\rm DD} = 10^{4}, v_{\rm D} = 3^{4}$		3.0		3.5	3.0		3.0	
		$V_{DD} = 150, v_0 = 15.00$		1						
VIII	HIGH Level Input Voltage	$\mu_0 < 1 \mu_0$	3.5		3.5	2.75		3.5		
	(CD4050BC Only)		7.0		7.0	5.5		7.0		V
		$v_{DD} = 100, v_D = 30$	11.0		11.0	8.25		11.0		
		V _{DD} = 15V, V _D = 13.5V		-	-				T	
VIII	HIGH Level Input Voltage	$ \mathbf{b} \le 1 \mu \mathbf{A}$	4.0		4.0	3.5		4.0		
	(CD4049UBC Only)	$v_{DD} = 3v, v_O = 0.5v$	80		8.0	7.5		8.0		1
		$v_{DD} = 100, v_0 = 100$	12.	0	12.0	11.5		12.0		
		$V_{DD} = 15V, V_{D} = 1.5V$								
lot.	LOW Level Output Current	$V_{III} = V_{DD}, V_{II} = 0V$	51		4.6	5		3.2		
	(Note 4)	$v_{DD} = 5V, v_O = 0.4V$	15	2	9.8	12		6.8	3	п
		$V_{DD} = 10V, V_D = 0.5V$	3		29	40		20		
		$V_{DD} = 15V, V_D = 1.5V$				-				
юн	HIGH Level Output Current	$V_{IH} = V_{DD}, V_{IL} = 0V$		2	-1	-1	6	-0.7	72	
	(Note 4)	$V_{\rm DD}=5V, V_{\rm O}=4.6V$	-1		2	2 _2	6	-1.	5	1
		$V_{DD} = 10V. V_0 = 9.5V$	-2	0	_7	2 -1	2	-	5	
		$V_{DD} = 15V, V_{\bar{D}} = 13.5V$	-2		4	10	-0 -1	0.1	-1	.0
lune	Input Current	$V_{DD} = 15V, V_{IN} = 0V$				10	-5 (0.1	1	.0
-41%		$V_{DD} = 15V, V_{HI} = 15V$							_	

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DC Electrical Characteristics (Continued)

Note 4: These are peak output current capabilities. Continuous output current is rated at 12 mA maximum. The output current should not be allowed to exceed this value for extended periods of time. Including the tested one output at a time.

AC Electrical Characteristics (Note 5)

CD4049UBC $T_A = 25^{\circ}\text{C}, \text{ C}_L = 50 \text{ pF}, \text{R}_L = 200\text{k}, t_f = t_f = 20 \text{ ns}, \text{ unless otherwise specified}$

Symbol	Parameter	Conditions	Man	iyp	INGA	4.1110
to a	Pronagation Delay Time	$V_{DD} = 5V$		30	65	
424-41.	HIGH IN OW Level	Vnn = 10V		20	40	ກຣ
	HIGH-LOTT LOTO	Von = 15V		15	-30	
	Descention Dolay Time	Vnn = 5V		45	85	
4PLH	Propagation Detay Time	$V_{mn} = 10V$		25	45	ns
	LOW-to-HIGH Level	$V_{\rm D} = 15V$		20	35	
		900-100 March 51/		30	60	
tTH.	Transition Time	VDD=30		20	40	ns
	HIGH-IO-LOW Level	VDD = 10V		15	30	
		$v_{DD} = 15$		60	120	
ITLH	Transition Time	$V_{DD} = 5V$		30	55	ns
-	LOW-to-HIGH Level	$V_{DD} = 10V$		25	45	-
		$V_{DD} = 15V$		15	22.5	pF
Cal	Input Capacitance	Any Input		10	66.0	

Note 5: AC Parameters are guaranteed by DC correlated testing.

AC Electrical Characteristics (Note 6)

CD4050BC

200k $t_{r} = t_{r} = 20$ ns, unless otherwise specified

Parameter	Conditions	Min	Тур	Nax	Units
Fallalleter	V = 5V	_	60	110	
Propagation Delay Time	400 - 34		25	55	ns
HIGH-to-LOW Level	$V_{DD} = 10V$		20	30	
	V _{DD} = 154		60	120	
Propagation Delay Time	$V_{\rm ed} = 10V$		30	55	ns
LOW-to-HIGH Level	$V_{\rm ED} = 15V$		25	45	
The Time	Vro = 5V		30	60	
transmon time	Ven = 10V		20	40	ns
HIGH-ID-LOW LOAM	$V_{PO} = 15V$	-	15	30	
Transition Time	Vnn = 5V		60	120	
Hansson Hine	$V_{\rm rec} = 10V$		30	55	ns
LOXA-to-LIQLI Fead	$V_{\rm rep} = 15V$		25	45	
In ant Conneitance	Any Input		5	7.5	pF
	SUPT, NL - 2004, 4 - 4 Parameter Propagation Delay Time HIGH-to-LOW Level Propagation Delay Time LOW-to-HIGH Level Transition Time HIGH-to-LOW Level Transition Time LOW-to-HIGH Level low4 Caracitance	$\begin{tabular}{ c c c c } \hline Parameter & Conditions \\ \hline Propagation Delay Time & V_{ED} = 5V \\ \hline HIGH-to-LOW Level & V_{ED} = 10V \\ \hline V_{ED} = 15V \\ \hline Propagation Delay Time & V_{ED} = 5V \\ \hline LOW-to-HIGH Level & V_{ED} = 10V \\ \hline V_{ED} = 15V \\ \hline Transition Time & V_{ED} = 5V \\ \hline HIGH-to-LOW Level & V_{ED} = 5V \\ \hline HIGH-to-LOW Level & V_{ED} = 5V \\ \hline Transition Time & V_{ED} = 5V \\ \hline Transition Time & V_{ED} = 5V \\ \hline LOW-to-HIGH Level & V_{ED} = 10V \\ \hline V_{ED} = 15V \\ \hline Transition Time & V_{ED} = 5V \\ \hline LOW-to-HIGH Level & V_{ED} = 10V \\ \hline V_{ED} = 15V \\ \hline Transition Time & V_{ED} = 5V \\ \hline LOW-to-HIGH Level & V_{ED} = 10V \\ \hline V_{ED} = 15V \\ \hline Transition Time & V_{ED} = 10V \\ \hline V_{ED} = 15V \\ \hline Transition Time & V_{ED} = 10V \\ \hline V_{ED} = 15V \\ \hline Transition Time & V_{ED} = 10V \\ \hline V_{ED} = 15V \\ \hline Transition Time & V_{ED} = 10V \\ \hline V_{ED} = 15V \\ \hline Transition Time & V_{ED} = 10V $	$\begin{tabular}{ c c c c c } \hline Parameter & Conditions & Min \\ \hline Propagation Delay Time & V_{DD} = 5V \\ \hline HIGH-to-LOW Level & V_{DD} = 10V \\ \hline V_{DD} = 15V \\ \hline Propagation Delay Time & V_{DD} = 5V \\ \hline LOW-to-HIGH Level & V_{DD} = 10V \\ \hline V_{DD} = 15V \\ \hline Transition Time & V_{DD} = 5V \\ \hline HIGH-to-LOW Level & V_{DD} = 5V \\ \hline HIGH-to-LOW Level & V_{DD} = 10V \\ \hline V_{DD} = 15V \\ \hline Transition Time & V_{ED} = 5V \\ \hline LOW-to-HIGH Level & V_{ED} = 5V \\ \hline LOW-to-HIGH Level & V_{ED} = 10V \\ \hline V_{ED} = 15V \\ \hline Transition Time & V_{ED} = 5V \\ \hline LOW-to-HIGH Level & V_{ED} = 10V \\ \hline V_{ED} = 15V \\ \hline \end{tabular}$	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{ c c c c c c } \hline \mbox{Parameter} & \mbox{Conditions} & \mbox{Min} & \mbox{Typ} & \mbox{Max} \\ \hline \mbox{Propagation Delay Time} & \mbox{V}_{DD} = 5V & & \mbox{C}_{DD} = 10V & & \mbox{25} & 55 & \\ \mbox{V}_{DD} = 15V & & \mbox{20} & 30 & \\ \hline \mbox{Propagation Delay Time} & \mbox{V}_{DD} = 5V & & \mbox{60} & 120 & \\ \mbox{V}_{DD} = 15V & & \mbox{20} & 30 & 55 & \\ \mbox{LOW-to-HIGH Level} & \mbox{V}_{DD} = 10V & & \mbox{25} & 45 & \\ \mbox{V}_{DD} = 15V & & \mbox{20} & 30 & 60 & \\ \mbox{V}_{DD} = 15V & & \mbox{20} & 40 & \\ \mbox{V}_{DD} = 15V & & \mbox{20} & 40 & \\ \mbox{V}_{DD} = 15V & & \mbox{20} & 40 & \\ \mbox{V}_{DD} = 15V & & \mbox{20} & 40 & \\ \mbox{V}_{DD} = 15V & & \mbox{20} & 40 & \\ \mbox{V}_{DD} = 15V & & \mbox{20} & 40 & \\ \mbox{V}_{DD} = 15V & & \mbox{20} & 40 & \\ \mbox{V}_{DD} = 15V & & \mbox{20} & 55 & \\ \mbox{LOW-to-HIGH Level} & \mbox{V}_{DD} = 5V & & \mbox{20} & 55 & \\ \mbox{V}_{DD} = 15V & & \mbox{20} & 55 & \\ \mbox{V}_{DD} = 15V & & \mbox{20} & 55 & \\ \mbox{V}_{DD} = 15V & & \mbox{20} & 55 & \\ \mbox{V}_{DD} = 15V & & \mbox{25} & 45 & \\ \mbox{V}_{DD} = 15V & & $

Note 6: AC Parameters are guaranteed by DC correlated testing.

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ISO²-CMOS MT8870D/MT8870D-1 Integrated DTMF Receiver

Features

- Complete DTMF Receiver
- Low power consumption
- Internal gain setting amplifier
- Adjustable guard time
- Central office quality
- Power-down mode
- Inhibit mode
- Backward compatible with MT8870C/MT8870C-1

Applications

- Receiver system for British Telecom (BT) or CEPT Spec (MT8870D-1)
- Paging systems
- Repeater systems/mobile radio
- Credit card systems
- Remote control
- Personal computers
- Telephone answering machine

Ordering	Information							
MT8870DE/DE-1	18 Pin Plastic DIP							
MT8870DS/DS-1	18 Pin SOIC							
MT8870DN/DN-1	20 Pin SSOP							
-40 °C to +85 °C								

ISSUE 5

March 1997

Description

The MT8870D/MT8870D-1 is a complete DTMF receiver integrating both the bandsplit filter and digital decoder functions. The filter section uses switched capacitor techniques for high and low group filters; the decoder uses digital counting techniques to detect and decode all 16 DTMF tone-pairs into a 4-bit code. External component count is minimized by on chip provision of a differential input amplifier, clock oscillator and latched three-state bus interface.



5870D/MT8870D-1 ISO2-CMOS



Figure 2 - Pin Connections

Description

-	= 7		
-	20	Name	Description
	1	IN+	Non-Inverting Op-Amp (Input).
	2	IN-	Inverting Op-Amp (Input).
	3	GS	Gain Select. Gives access to output of front end differential amplifier for connection of feedback resistor.
18	4	V _{Ref}	Reference Voltage (Output). Nominally $V_{DD}/2$ is used to bias inputs at mid-rail (see Fig. 6 and Fig. 10).
	5	INH	Inhibit (Input). Logic high inhibits the detection of tones representing characters A, B, C and D. This pin input is internally pulled down.
	6	PWDN	Power Down (Input). Active high. Powers down the device and inhibits the oscillator. This pin input is internally pulled down.
1	8	OSC1	Clock (Input).
	9	OSC2	Clock (Output). A 3.579545 MHz crystal connected between pins OSC1 and OSC2 completes the internal oscillator circuit.
1940	10	V _{SS}	Ground (Input). 0V typical.
10	11	TOE	Three State Output Enable (Input). Logic high enables the outputs Q1-Q4. This pin is pulled up internally.
16.25	12- 15	Q1-Q4	Three State Data (Output). When enabled by TOE, provide the code corresponding to the last valid tone-pair received (see Table 1). When TOE is logic low, the data outputs are high impedance.
NO.	17	StD	Delayed Steering (Output) .Presents a logic high when a received tone-pair has been registered and the output latch updated; returns to logic low when the voltage on St/GT falls below V_{TSt} .
10	18	ESt	Early Steering (Output). Presents a logic high once the digital algorithm has detected a valid tone pair (signal condition). Any momentary loss of signal condition will cause ESt to return to a logic low.
17	19	St/GT	Steering Input/Guard time (Output) Bidirectional. A voltage greater than V_{TSt} detected at St causes the device to register the detected tone pair and update the output latch. A voltage less than V_{TSt} frees the device to accept a new tone pair. The GT output acts to reset the external steering time-constant; its state is a function of ESt and the voltage on St.
100	20	V _{DD}	Positive power supply (Input). +5V typical.
	7, 16	NC	No Connection.

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Functional Description

The MT8870D/MT8870D-1 monolithic DTMF receiver offers small size, low power consumption and high performance. Its architecture consists of a bandsplit filter section, which separates the high and low group tones, followed by a digital counting section which verifies the frequency and duration of the received tones before passing the corresponding code to the output bus.

Filter Section

Separation of the low-group and high group tones is achieved by applying the DTMF signal to the inputs of two sixth-order switched capacitor bandpass filters, the bandwidths of which correspond to the low and high group frequencies. The filter section also incorporates notches at 350 and 440 Hz for exceptional dial tone rejection (see Figure 3). Each filter output is followed by a single order switched capacitor filter section which smooths the signals prior to limiting. Limiting is performed by high-gain comparators which are provided with hysteresis to prevent detection of unwanted low-level signals. The putputs of the comparators provide full rail logic swings at the frequencies of the incoming DTMF signals.

Decoder Section

Following the filter section is a decoder employing digital counting techniques to determine the frequencies of the incoming tones and to verify that they correspond to standard DTMF frequencies. A complex averaging algorithm protects against tone simulation by extraneous signals such as voice while



providing tolerance to small frequency deviations and variations. This averaging algorithm has been developed to ensure an optimum combination of immunity to talk-off and tolerance to the presence of interfering frequencies (third tones) and noise. When the detector recognizes the presence of two valid tones (this is referred to as the "signal condition" in some industry specifications) the "Early Steering" (ESt) output will go to an active state. Any subsequent loss of signal condition will cause ESt to assume an inactive state (see "Steering Circuit").

Steering Circuit

Before registration of a decoded tone pair, the receiver checks for a valid signal duration (referred to as character recognition condition). This check is performed by an external RC time constant driven by ESt. A logic high on ESt causes v_c (see Figure 4) to rise as the capacitor discharges. Provided signal



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maintained (ESt remains high) for the period (t_{GTP}), v_c reaches the threshold me steering logic to register the tone pair, corresponding 4-bit code (see Table 1) the sutput latch. At this point the GT output is and drives vc to VDD. GT continues to drive er as long as ESt remains high. Finally, after a to allow the output latch to settle, the steering output flag (StD) goes high, that a received tone pair has been ed. The contents of the output latch are alable on the 4-bit output bus by raising the state control input (TOE) to a logic high. The circuit works in reverse to validate the pause between signals. Thus, as well as signals too short to be considered valid, the will tolerate signal interruptions (dropout) expect to be considered a valid pause. This facility, with the capability of selecting the steering the constants externally, allows the designer to set performance to meet a wide variety of system ements.

Eard Time Adjustment

any situations not requiring selection of tone and interdigital pause, the simple steering shown in Figure 4 is applicable. Component are chosen according to the formula:

$t_{REC} = t_{DP} + t_{GTP}$ $t_{ID} = t_{DA} + t_{GTA}$

and t_{REC} is the minimum signal duration to be sognized by the receiver. A value for C of 0.1 μ F is



Figure 5 - Guard Time Adjustment

Digit	TOF	INH	ESt	0,	Qa	Qa	Q1			
Digit	IUL	V		7	7	7	7			
ANY	L			2	2	0	- 1			
1	Н	X	н	0	0	0	1			
2	Н	Х	Н	0	0	1	0			
3	Н	Х	Н	0	0	1	1			
4	Н	х	Н	0	1	0	0			
5	н	Х	Н	0	1	0	1			
6	Н	Х	Н	0 [°]	1	1	0			
7	Н	Х	Н	0	1	1	1			
8	н	Х	н	1	0	0	0			
9	Н	X	Н	1	0	0	1			
0	н	Х	Н	1	0	1	0			
*	Н	Х	Н	1	0	1	1			
#	Н	X	н	· 1	1	0	0			
А	Н	L	н	1	1	0	1			
В	Н	L	н	1	1	1	0			
С	н	L	Н	1	1	1	1			
D	Н	L	н	0	- 0	0	0			
А	Н	н	L							
В	н	Н	L	undete	cted, th main th	ie outp e same	as the			
С	н	Н	L	previou	us detect	ted code				
D	Н	н	L							
	-	11-4	F	Land	Deeec	la Tab	0			

L=LOGIC LOW, H=LOGIC HIGH, Z=HIGH IMPEDANCE X = DON'T CARE

recommended for most applications, leaving R to be selected by the designer.

Different steering arrangements may be used to select independently the guard times for tone present (t_{GTP}) and tone absent (t_{GTA}) . This may be necessary to meet system specifications which place both accept and reject limits on both tone duration and interdigital pause. Guard time adjustment also allows the designer to tailor system parameters such as talk off and noise immunity. Increasing tREC improves talk-off performance since it reduces the probability that tones simulated by speech will maintain signal condition long enough to be registered. Alternatively, a relatively short tREC with a long t_{DO} would be appropriate for extremely noisy environments where fast acquisition time and immunity to tone drop-outs are required. Design information for guard time adjustment is shown in Figure 5.

Power-down and Inhibit Mode

A logic high applied to pin 6 (PWDN) will power down be device to minimize the power consumption in a standby mode. It stops the oscillator and the functions of the filters.

conhibit mode is enabled by a logic high input to the pin 5 (INH). It inhibits the detection of tones representing characters A, B, C, and D. The output code will remain the same as the previous detected code (see Table 1).

Differential Input Configuration

The input arrangement of the MT8870D/MT8870D-1 provides a differential-input operational amplifier as well as a bias source (V_{Ref}) which is used to bias the inputs at mid-rail. Provision is made for connection of a feedback resistor to the op-amp output (GS) for adjustment of gain. In a single-ended configuration, the input pins are connected as shown in Figure 10 with the op-amp connected for unity gain and V_{Ref} biasing the input at $1/_2$ V_{DD}. Figure 6 shows the differential configuration, which permits the adjustment of gain with the feedback resistor R₅.

Crystal Oscillator

The internal clock circuit is completed with the addition of an external 3.579545 MHz crystal and is normally connected as shown in Figure 10 (Single-Ended Input Configuration). However, it is possible to configure several MT8870D/MT8870D-1 devices employing only a single oscillator crystal. The oscillator output of the first device in the chain is coupled through a 30 pF capacitor to the oscillator input (OSC1) of the next device. Subsequent devices are connected in a similar fashion. Refer to Figure 7 The problems associated with for details. unbalanced loading are not a concern with the arrangement shown, i.e., precision balancing capacitors are not required.



Figure 6 - Differential Input Configuration



Figure 7 - Oscillator Connection

Parameter	Unit	Resonator
R1	Ohms	10.752
L1	mH	.432
C1	pF	4.984
CO	pF	37.915
Qm	-	896.37
Δf	%	±0.2%

 Table 2. Recommended Resonator Specifications

 Note: Qm=quality factor of RLC model, i.e., 1/2ПfR1C1.

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shown in Fig. 9 illustrates the use of device in a typical receiver system. BT is the input signals less than -34 dBm as a suitable values of R_1 and R_2 to a suitable values of R_1 and R_2 to a suitable values of R_1 and R_2 to a strenuation, such that -34 dBm input correspond to -37 dBm at the gain setting T8870D-1. As shown in the diagram, the values of R_3 and C_2 are the guard time is when the total component tolerance is better performance, it is recommended to con-symmetric guard time circuit in Fig. 8.





Figure 9 - Single-Ended Input Configuration for BT or CEPT Spec

Parameter	Symbol	Min	Max	Units
Falameter	-			
	N/		7	V
C Power Supply Voltage	V DD		1/-+0.3	V
	VI	V _{SS} -0.3	VDD10.0	
Voltage on any pin	h		10	mA
Current at any pin (other than supply)		65	+150	°C
Oterese tomperature	T _{STG}	-00		101
Storage temperature	Pn		500	mvv
Package power dissipation	naration under these	conditions is not i	mplied.	

rating Conditions - Voltages are with respect to ground (V_{SS}) unless otherwise stated.

Fecommended Operating Conditions					_	Inite	Tost Conditions	
	Parameter	Sym	Min	Тур‡	Max	Units	Test conditione	
_		Vpp	4.75	5.0	5.25	V		
t	DC Power Supply Voltage		10		+85	°C		
2	Operating Temperature	10	-40	2 570545		MHZ		
3	Crystal/Clock Frequency	fc		3.579545		0/		
	Crystal/Clock Freg.Tolerance	∆fc		±0.1		%	1	

Typical figures are at 25°C and are for design aid only: not guaranteed and not subject to production t

racteristics - V_{DD} =5.0V± 5%, V_{SS} =0V, -40°C ≤ T_O ≤ +85°C, unless otherwise stated.

CEI	ec	trical Gilaracteristics	Sym	Min	Typ [‡]	Max	Units	Test Conditions
		Characteristics	- J		10	25	μA	PWDN=V _{DD}
1 9	5 5	Standby supply current	DDQ		00	0.0	mA	
		Operating supply current	IDD	1	3.0	9.0		fo=3 579545 MHz
3 F		Power consumption	Po		15		mvv	10-3.373040 11112
	Y		V	35			V	V _{DD} =5.0V
1		High level input	VIH	0.0		15	V	V _{DD} =5.0V
5	Γ	Low level input voltage	VIL			1.0	μΔ	VIN=Ves Or VDD
3	T	Input leakage current	IIH/IIL		0.1		μη	TOE (pin 10)=0
7	N	Pull up (source) current	Iso		7.5	20	μΑ	V _{DD} =5.0V
8	P U T	Pull down (sink) current	I _{SI}		15	45	μΑ	INH=5.0V, PWDN=5.0V V _{DD} =5.0V
	S		-		10		MΩ	@ 1 kHz
9		Input impedance (IN+, IN-)	RIN		0.1	25	V	$V_{DD} = 5.0V$
10		Steering threshold voltage	V _{TSt}	2.2	2.4	2.5	V	Noload
11		Low level output voltage	VOL			V _{SS} +0.03	V	his load
10	0	High level output voltage	VOH	V _{DD} -0.03			V	NO IOAU
12	υ	Flightever output round	10	1.0	2.5		mA	V _{OUT} =0.4 V
13	T	Output low (sink) current	lou	0.4	0.8		mA	V _{OUT} =4.6 V
14	U	Output high (source) current	HOH	23	25	2.7	V	No load, V _{DD} = 5.0V
15	S	V _{Ref} output voltage	VRef	2.0	1		kΩ.	
10	1	V output resistance	ROR	1				

16 V_{Ref} outpu [‡] Typical figures are at 25°C and are for design aid only: not guaranteed and not subject to production testing.

Characteristics - V_{DD} =5.0V±5%, V_{SS} =0V, -40°C ≤ T_O ≤ +85°C ,unless otherwise stated. tting Amplifier

	Characteristics	Sym	Min	Typ‡	Max	Units	Test Conditions
	input leakage current	I _{IN}			100	nA	$V_{SS} \le V_{IN} \le V_{DD}$
	rout resistance	R _{IN}	10			MΩ	
	Input offset voltage	Vos			25	mV	
-	Power supply rejection	PSRR	50			dB	1 kHz
	Common mode rejection	CMRR	40			dB	$0.75~\text{V} \leq \text{V}_{\text{IN}} \leq 4.25~\text{V}$ biased at V_{Ref} =2.5 V
W.	DC open loop voltage gain	A _{VOL}	32			dB	
2	Unity gain bandwidth	f _C	0.30			MHz	
	Output voltage swing	Vo	4.0			V _{pp}	Load \geq 100 k Ω to V _{SS} @ GS
	Maximum capacitive load (GS)	CL			100	pF	
10	Resistive load (GS)	RL			50	kΩ	
11	Common mode range	V _{CM}	2.5			V _{pp}	No Load

WT3870D AC Electrical Characteristics - V_{DD} =5.0V ±5%, V_{SS} =0V, -40°C ≤ T_O ≤ +85°C, using Test Circuit shown in Figure 10.

	Characteristics	Sym	Min	Тур‡	Max	Units	Notes*
	Valid input signal levels (each tone of composite signal)		-29		+1	dBm	1,2,3,5,6,9
			27.5		869	mV _{RMS}	1,2,3,5,6,9
2	Negative twist accept				8	dB	2,3,6,9,12
з	Positive twist accept				8	dB	2,3,6,9,12
4	Frequency deviation accept		±1.5% ± 2 Hz				2,3,5,9
5	Frequency deviation reject		±3.5%				2,3,5,9
6	Third tone tolerance			-16		dB	2,3,4,5,9,10
7	Noise tolerance			-12		dB	2,3,4,5,7,9,10
=	Dial tone tolerance			+22		dB	2,3,4,5,8,9,11

cal figures are at 25 °C and are for design aid only: not guaranteed and not subject to production testing.

OTES Bin= decibels above or below a reference power of 1 mW into a 600 ohm load. Digit sequence consists of all DTMF tones. Tone duration= 40 ms, tone pause= 40 ms. Signal condition consists of nominal DTMF frequencies. Both tones in composite signal have an equal amplitude. Tone pair is deviated by ± 1.5 % ± 2 Hz. Bandwidth limited (3 kHz) Gaussian noise. The precise dial tone frequencies are (350 Hz and 440 Hz) ± 2 %. For an error rate of better than 1 in 10,000. Referenced to lowest level frequency component in DTMF signal. Referenced to the minimum valid accept level. Guaranteed by design and characterization.

-	in right to.								
	Characteristics	Sym	Min	Тур‡	Max	Units	Notes*		
1	Valid input signal levels (each tone of composite signal)		-31		+1	dBm	Tested at V _{DD} =5.0V		
			21.8		869	mV _{RMS}	1,2,3,5,6,9		
2	Input Signal Level Reject		-37			dBm	Tested at V _{DD} =5.0V		
-			10.9			mV _{RMS}	1,2,3,5,6,9		
3	Negative twist accept				8	dB	2,3,6,9,13		
4	Positive twist accept				8	dB	2,3,6,9,13		
5	Frequency deviation accept		±1.5%± 2 Hz				2,3,5,9		
6	Frequency deviation reject		±3.5%	1			2,3,5,9		
7	Third zone tolerance			-18.5		dB	2,3,4,5,9,12		
8	Noise tolerance			-12		dB	2,3,4,5,7,9,10		
9	Dial tone tolerance			+22		dB	2,3,4,5,8,9,11		

MT8870D-1 AC Electrical Characteristics - V_{DD} =5.0V±5%, V_{SS} =0V, -40°C \leq T_O \leq +85°C, using Test Circuit shown

in Figure 10

‡ Typical figures are at 25 °C and are for design aid only: not guaranteed and not subject to production testing.

*NOTES

*NOTES
1. dBm= decibels above or below a reference power of 1 mW into a 600 ohm load.
2. Digit sequence consists of all DTMF tones.
3. Tone duration= 40 ms, tone pause= 40 ms.
4. Signal condition consists of nominal DTMF frequencies.
5. Both tones in composite signal have an equal amplitude.
6. Tone pair is deviated by ±1.5 %±2 Hz.
7. Bandwidth limited (3 kHz) Gaussian noise.
8. The precise dial tone frequencies are (350 Hz and 440 Hz) ±2 %.
9. For an error rate of better than 1 in 10,000.
10. Referenced to lowest level frequency component in DTMF signal.
11. Referenced to Fig. 10 input DTMF tone level at -25dBm (-28dBm at GS Pin) interference frequency range between 480-3400Hz.
13. Guaranteed by design and characterization.

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		Characteristics	Sym	Min	Typ [‡]	Max	Units	Conditions
1		Tone present detect time	t _{DP}	5	11	14	ms	Note 1
2	Т	Tone absent detect time	t _{DA}	0.5	4	8.5	ms	Note 1
3	- M - Z G	Tone duration accept	tREC			40	ms	Note 2
4		Tone duration reject	TREC	20			ms	Note 2
5		Interdigit pause accept	t _{ID}			40	ms	Note 2
6		Interdigit pause reject	t _{DO}	20			ms	Note 2
7		Propagation delay (St to Q)	t _{PQ}		8	11	μs	TOE=VDD
8	0	Propagation delay (St to StD)	t _{PStD}		12	16	μs	TOE=V _{DD}
9	T	Output data set up (Q to StD)	t _{QStD}	- 3	3.4		μs	TOE=V _{DD}
10	P U T	Propagation delay (TOE to Q ENABLE)	t _{PTE}		50		ns	load of 10 kΩ, 50 pF
11	5	Propagation delay (TOE to Q DISABLE)	t _{PTD}		300		ns	load of 10 kΩ, 50 pF
2	P	Power-up time	t _{PU}		30		ms	Note 3
13	W N	Power-down time	t _{PD}		20		ms	
14		Crystal/clock frequency	f _C	3.5759	3.5795	3.5831	MHz	
15	CLOC	Clock input rise time	tLHCL			110	ns	Ext. clock
16		Clock input fall time	t _{HLCL}			110	ns	Ext. clock
17	К	Clock input duty cycle	DCCL	40	50	60	%	Ext. clock
18		Capacitive load (OSC2)	CLO		-	30	pF	

AC Electrical Characteristics - V_{DD} =5.0V±5%, V_{SS} =0V, -40°C \leq To \leq +85°C , using Test Circuit shown in Figure 10.

cal figures are at 25°C and are for design aid only: not guaranteed and not subject to production testing.

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S: Used for guard-time calculation purposes only. These, user adjustable parameters, are not device specifications. The adjustable settings of these minimums and maximums are recommendations based upon network requirements. With valid tone present at input, t_{PU} equals time from PDWN going low until ESt going high.



Figure 10 - Single-Ended Input Configuration

The 555 timer



Figure: The 555 internal circuit

The 555 circuit is consisted by two comparators, one ohmic ladder one flip-flop and a discharging transistor, as it is shown in figure 1.1.



Figure: The 555 modes of operation a) monostable b) astable (multivibrator).

This circuit can be connected as a monostable multivibrator or an astable multivibrator. The 555, connected as a monostable is shown in figure <u>1.1a</u>. In this mode of operation the *trigger* input sets the flip flop which drives the output to *high*. The discharge transistor is turned off and therefore the capacitor Ct is charged via Rt. When the voltage on the capacitor (Ct) reaches the control voltage, which is defined by the three resistor voltage divider (Vcont=2/3)

the flip-flop is resetted. This turns the discharge transistor on, which discharge the constitution. Thereafter the circuit can be charged again by a new pulse at the *trigger* input. The period is given by the equation:

T=1.1 Rt * Ct

There T is the output pulse high period, Ct the charging capacitance measured in Farads and Rt the charging resistor in Ohms.

the circuit is connected as an astable multivibrator (figure <u>1.1</u>b), the comparator 2 of figure sets the flip-flop, when the voltage on the capacitor Ct falls below 1/3Vcc, while the comparator 1 resets the flip-flop when the voltage on the capacitor becomes bigger than 23Vcc. In this case the discharging transistor is turned *on*, which discharge the time capacitor Ct via Rb.

This allows the use of the 555 as an oscillator (figure 1.1b) The time at the high (or charging) period is given by the equation:

Th=0.7(Ra+Rb)Ct

While the time for the low period is given by the equation:

Tl=0.7 Rb*Ct

The obvious observation from the above equations is that the duty cycle of the oscillator is always bigger than 50%. Or in other words the charging time is always bigger that the discharging period, since Ra+Rb>Rb taken in account that Ra>0. Yet if Ra>>Rb then a 50% duty cycle can be approximated.

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